

Semiconductors in high THz fields

Stephan Winnerl

Helmholtz-Zentrum Dresden-Rossendorf, Dresden - Germany

Heraeus Seminar
April 10-13, 2012
Bad Honnef



Mitglied der Helmholtz-Gemeinschaft

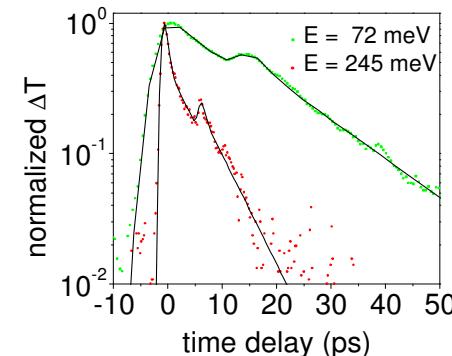
Stephan Winnerl | Institute of Ion Beam Physics and Materials Research | Spectroscopy Devision



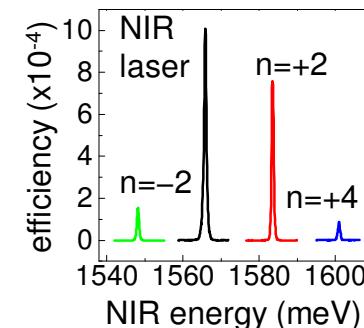
Outline

1. Motivation

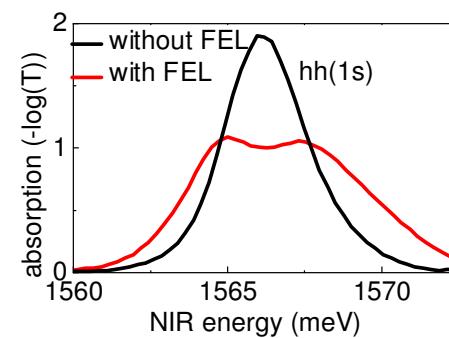
2. Population dynamics: pump-probe spectroscopy on graphene



3. Perturbative nonlinear interaction: sideband generation, excitons in semiconductor quantum wells



4. Nonperturbative regime: intraexcitonic AC Stark effect (Autler-Townes splitting)



5. Summary



Motivation

different regimes of nonlinear optics:

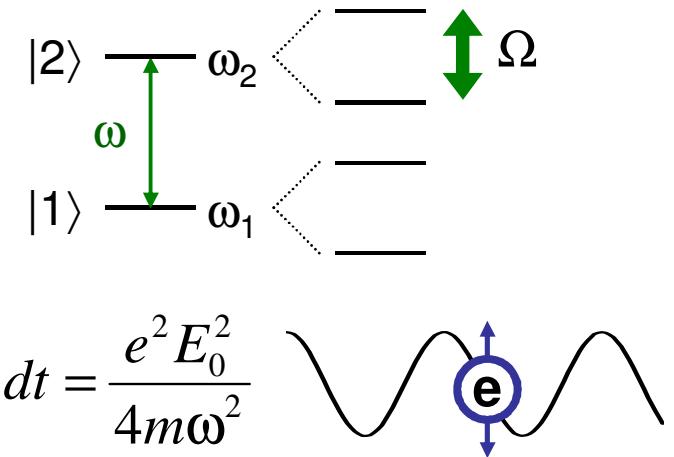
- **perturbative regime:** expansion in powers of electric field E
→ nonlinear susceptibilities $\chi^{(1)}$, $\chi^{(2)}$, $\chi^{(3)}$ etc.
- **non-perturbative regime:** finite population in excited states generated;
Rabi energy $\hbar\Omega = \mu E$ larger than broadening γ
→ dressed states
- **non-resonant high-field regime:** electric field so strong to modify the
„atomic“ potential:
 - electric-field induced ionization
 - high-harmonic generation ...



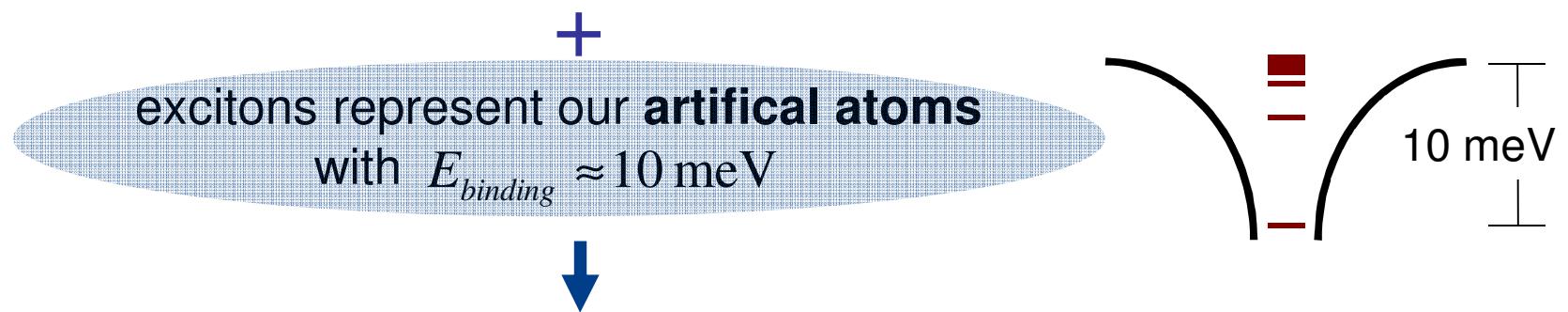
Motivation

energies/frequencies in light-matter coupling:

- photon energy & transition energy ω also binding energy
- coupling (Rabi) energy $\hbar\Omega = \mu E$
- ponderomotive energy $U_p = \frac{1}{T} \int_0^T \left(\frac{1}{2} mv^2 \right) dt = \frac{e^2 E_0^2}{4m\omega^2}$



In the **THz range** (1 THz = 4.1 meV) all of them can easily become of the order of 10 meV!



Unexplored regime!

Free-electron laser FELBE

Tuning range

FEL I $\lambda = 4 - 22 \mu\text{m}$

FEL II $\lambda = 18 - 250 \mu\text{m}$

⇒ 1 – 75 THz (5 – 310 meV)

Average power: 0.1 – 20 W

Spectral width: 0.5 – 2 %

Pulse energy: 0.1 – 2 μJ

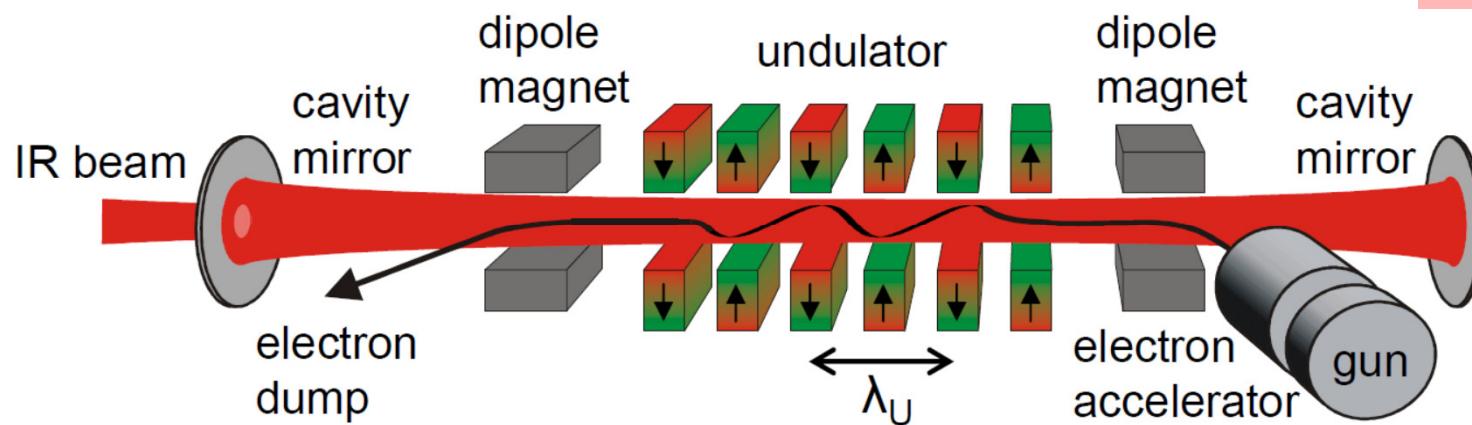
Pulse width: 1 – 25 ps

Repetition rate: 13 MHz

Only continuously pulsing FEL in Europe

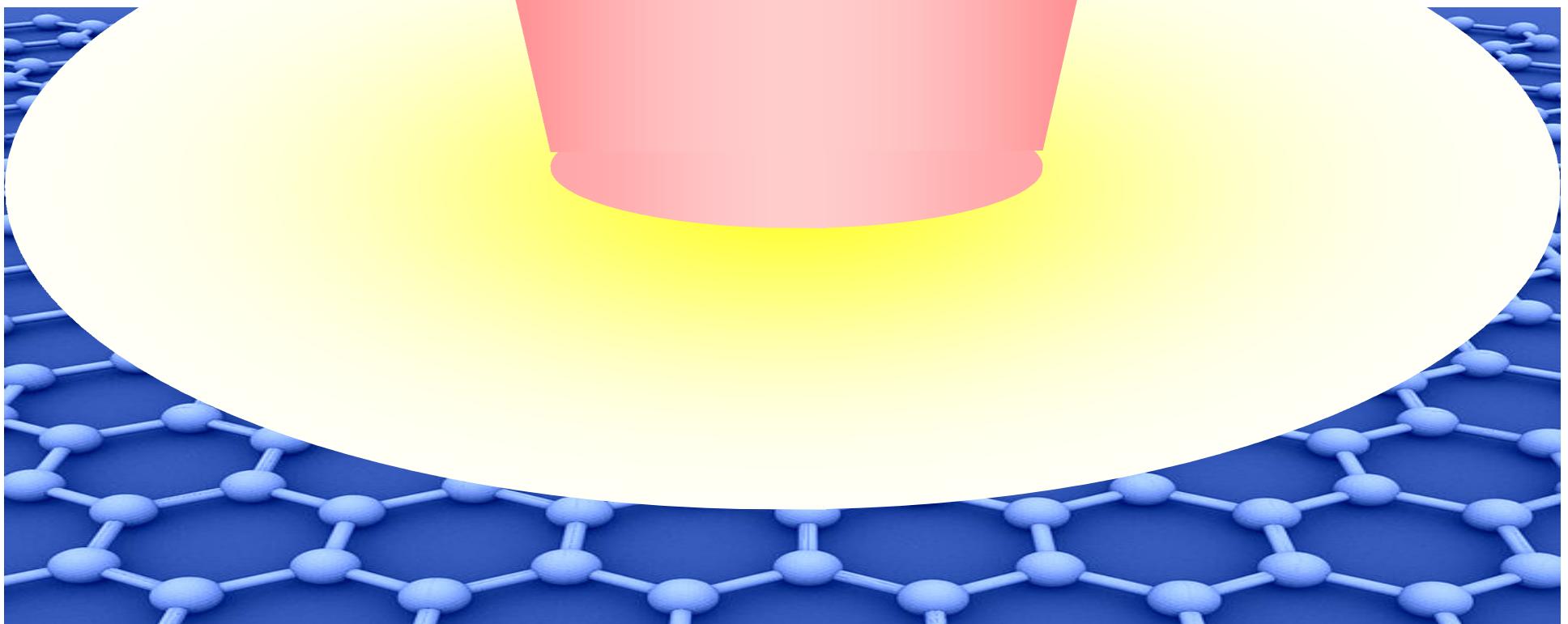


See Poster
FELBE facility



HZDR

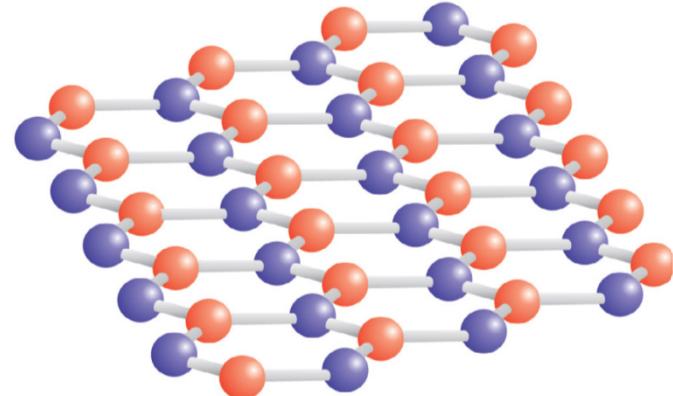
Population dynamics: carrier relaxation in graphene



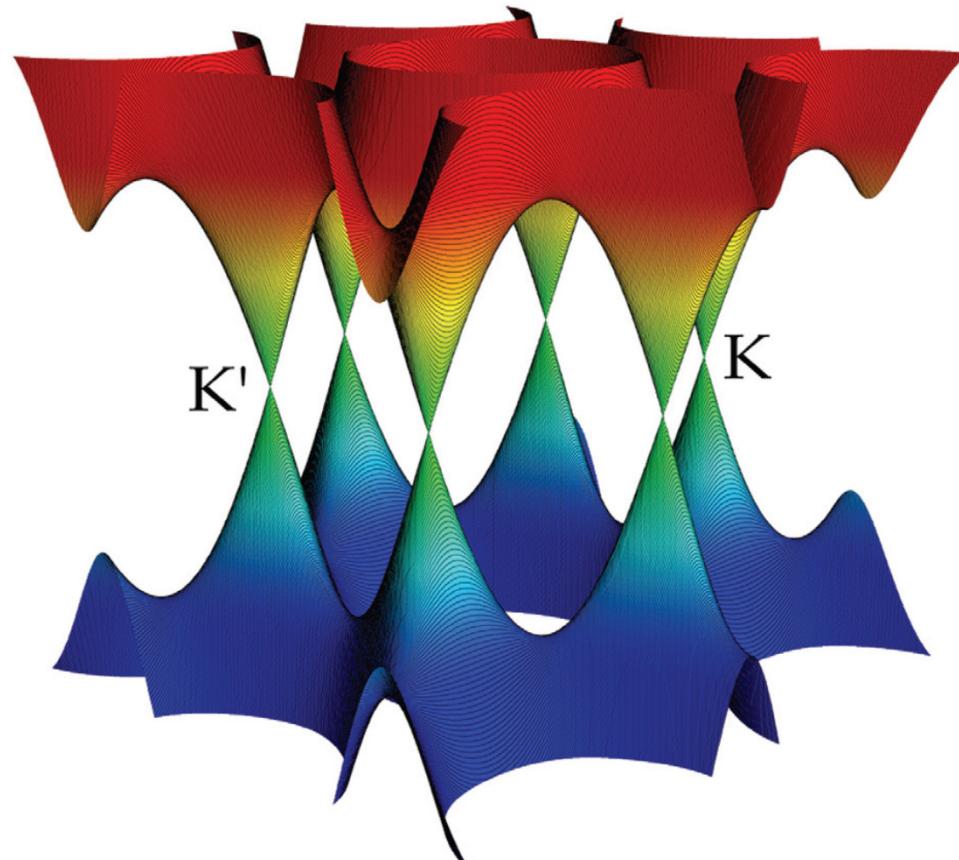


Introduction graphene

Graphene: mono-atomic layer of sp^2 bonded carbon atoms



Hexagonal structure,
two atoms per unit cell



Band structure with Dirac points

Images from M.I. Katsnelson, Materials Today **10**, 20 (2007)

Why study the carrier relaxation dynamics in graphene?

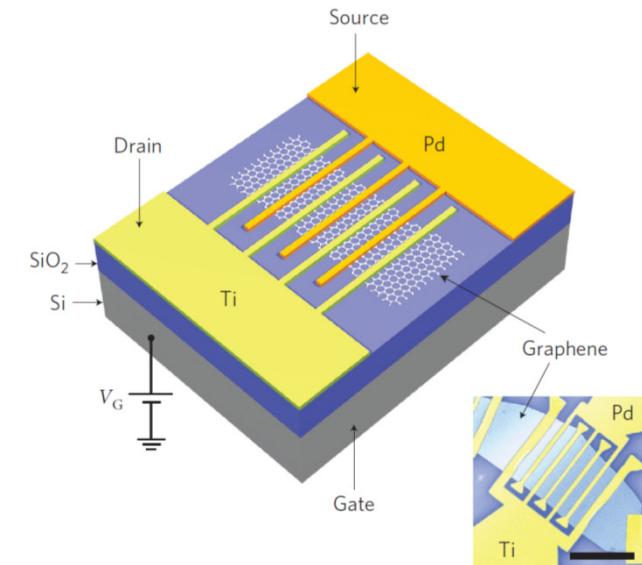
- Basic interest
 - Understanding of carrier dynamics, electron-phonon interaction,...
- Applications in optoelectronics
 - Conductive transparent coatings
 - Detectors, saturable absorbers
 - Novel THz devices
- **Previous studies: excitation at $E \approx 1.5$ eV**

*J.M. Dawlaty et al., APL **92**, 042116 (2008),*

*H. Wang et al., APL **96**, 081917 (2010),*

*D. Sun et al., PRL **104**, 136802 (2010),*

*M. Breusing et al., PRB **83**, 153410 (2011),...*



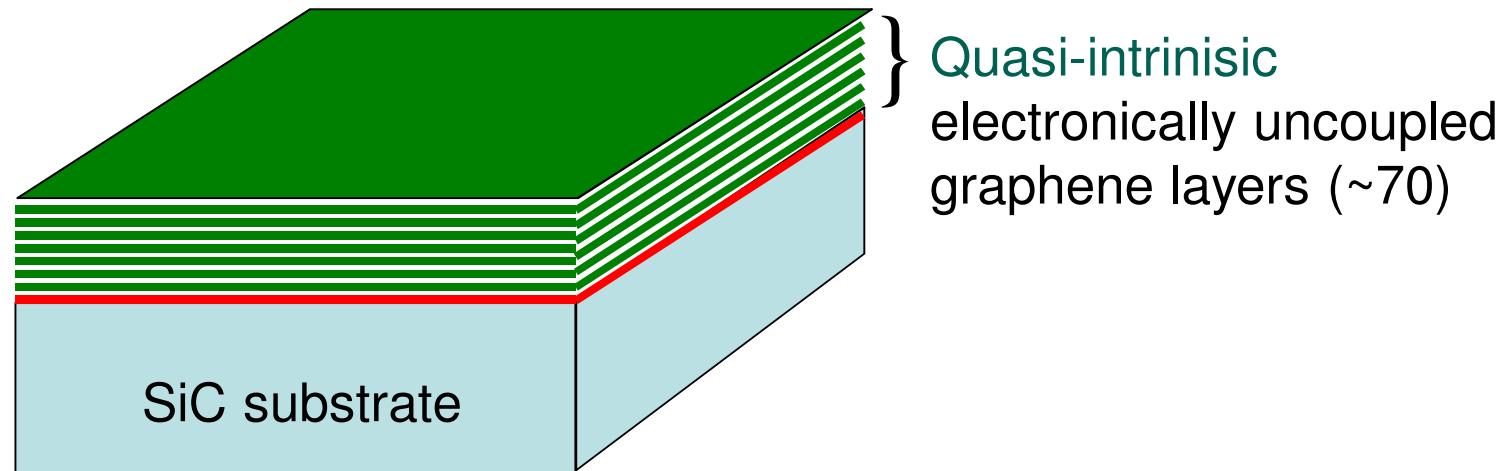
T. Mueller et al., Nature Photonics 2010

- **Focus of our study: low energy excitation, $E = 10 - 300$ meV**

Optical phonons (~ 200 meV), Fermi energy (~ 10 meV)



Our graphene samples

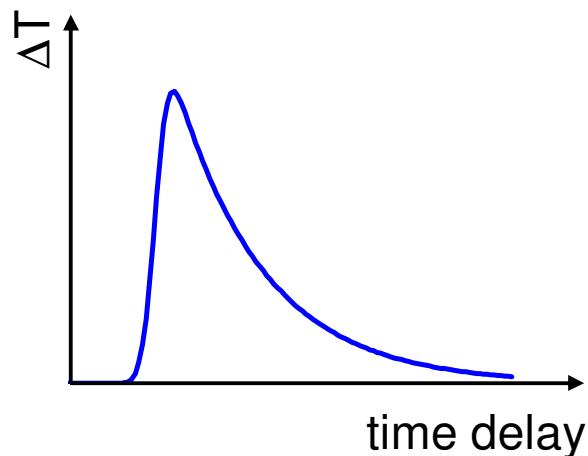
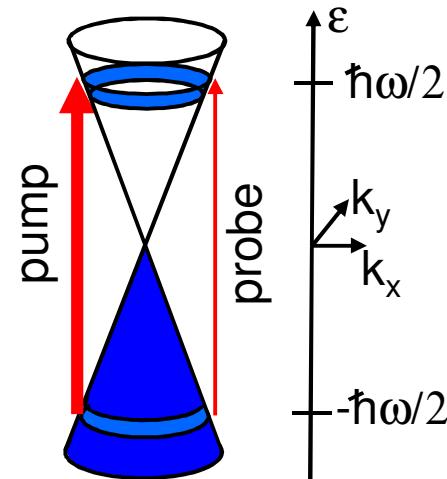
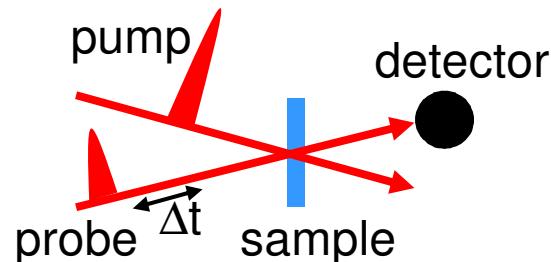


Epitaxial growth: thermal decomposition on the carbon terminated surface of 4H-SiC.

Samples well characterized by Raman spectroscopy and static magneto-spectroscopy.



Degenerate pump-probe spectroscopy on graphene



$$\frac{\Delta T}{T_0} \approx -\Delta\alpha(\hbar\omega) = -\alpha_0 \left(\Delta f_e\left(\frac{\hbar\omega}{2}\right) + \Delta f_h\left(-\frac{\hbar\omega}{2}\right) \right)$$

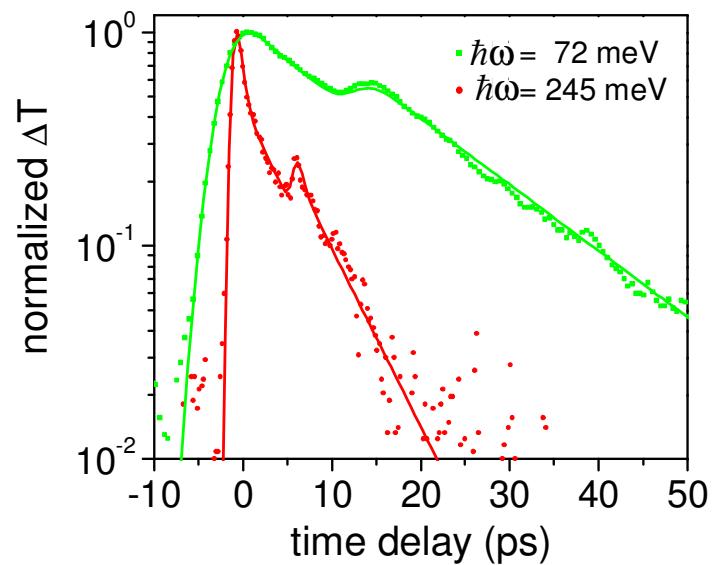
population dynamics

$$\alpha_0 = e^2/(4\epsilon_0\hbar c) \approx 2.3 \%$$

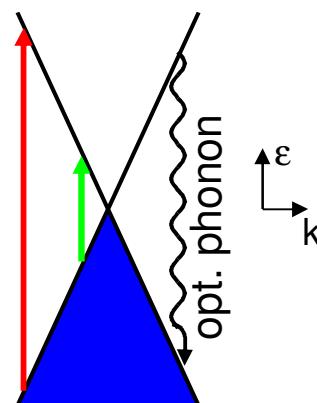
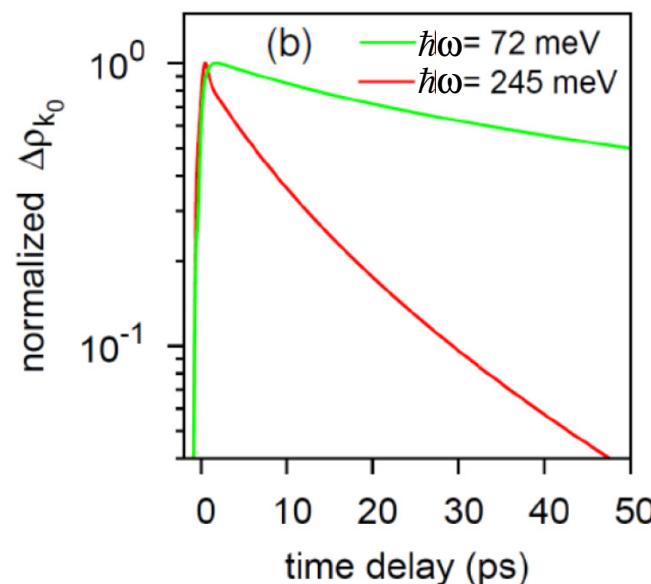


Pumping above and below the optical phonon energy

Experiment at FELBE



Microscopic theory (TU Berlin)



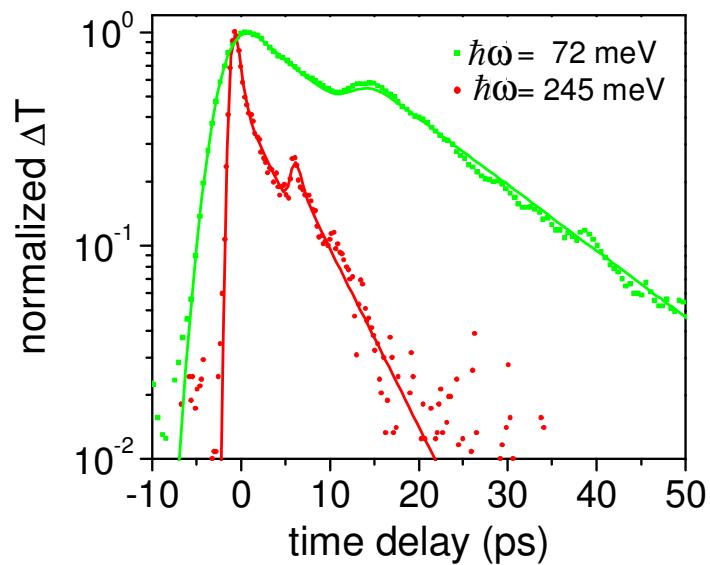
Slower relaxation for photon energies below the optical phonon energy ($\sim 200 \text{ meV}$)

S. Winnerl et al., Phys. Rev. Lett., **107**, 237401 (2011)

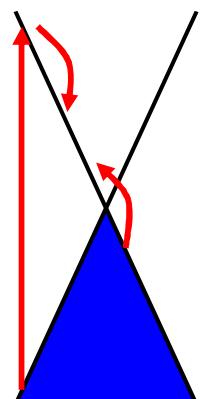
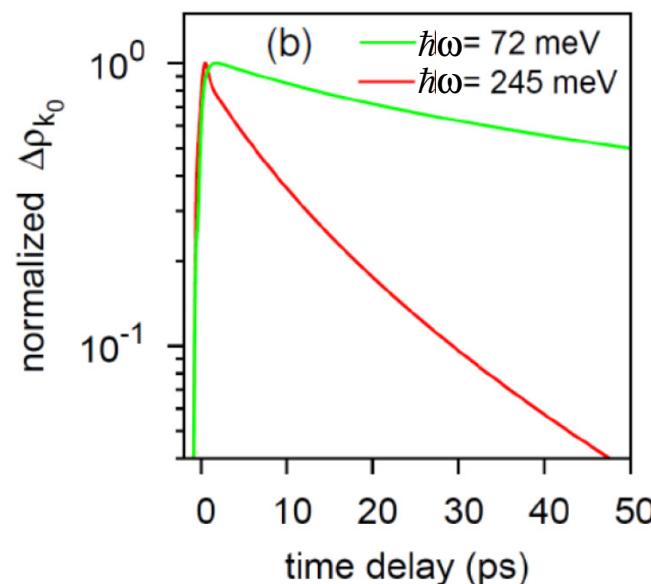


Pumping above and below the optical phonon energy

Experiment at FELBE



Microscopic theory (TU Berlin)



Slower relaxation for photon energies below the optical phonon energy ($\sim 200 \text{ meV}$)

Furthermore:

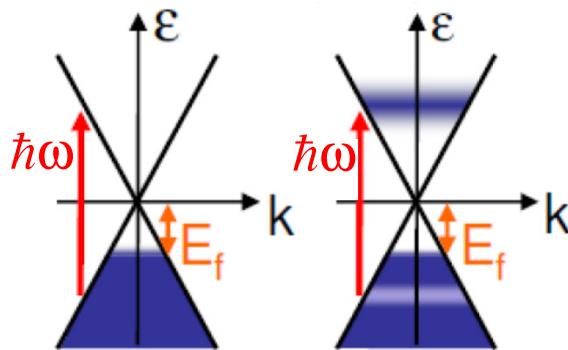
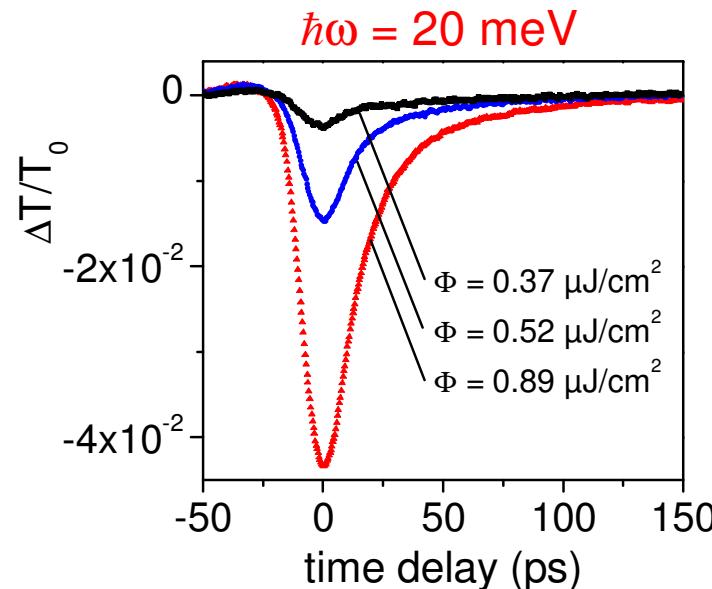
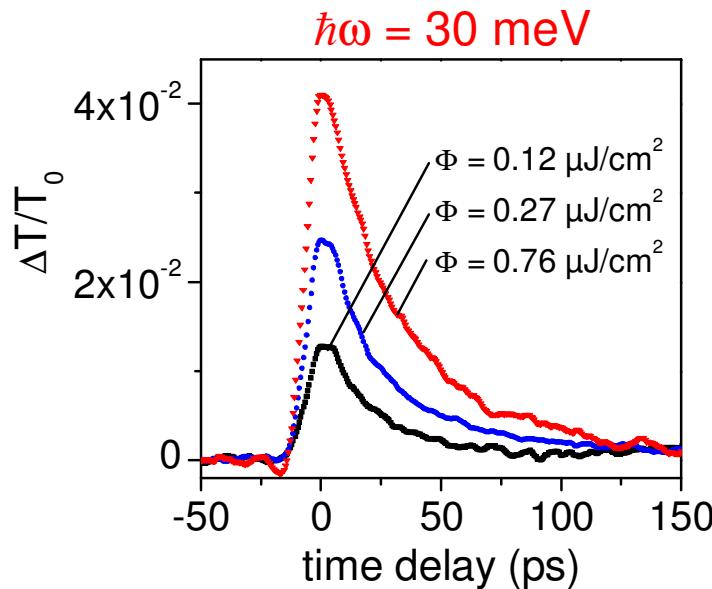
- Role of **Auger-type processes** ($\sim 1 \text{ ps}$ for $\hbar\omega = 245 \text{ meV}$)
- Acoustic phonons: $\tau \approx 300 \text{ ps}$

S. Winnerl et al., Phys. Rev. Lett., **107**, 237401 (2011)

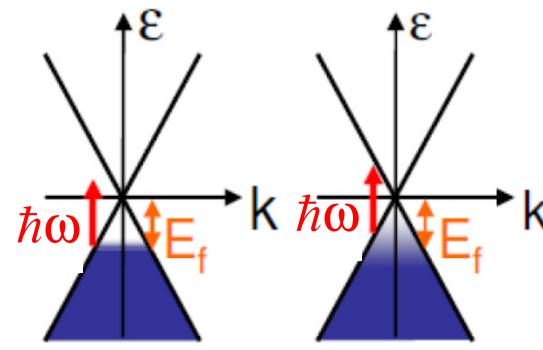




Sign reversal of pump-probe signal: Interplay of pump-induced transmission and absorption



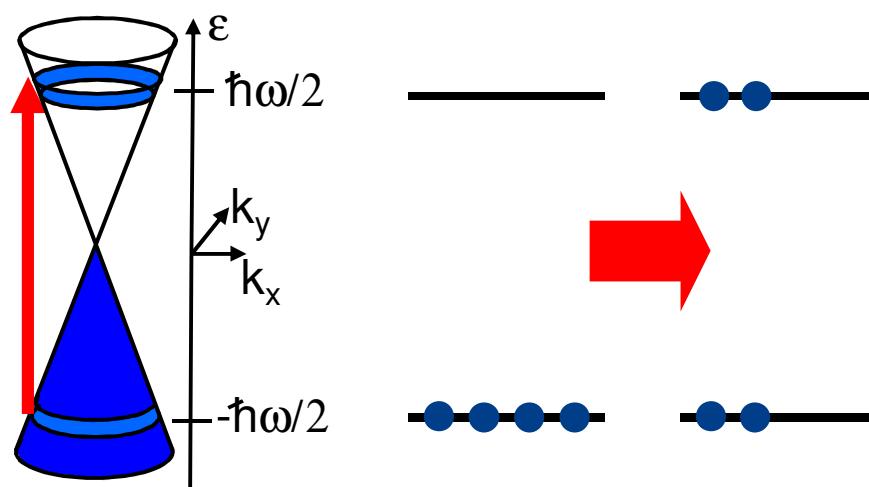
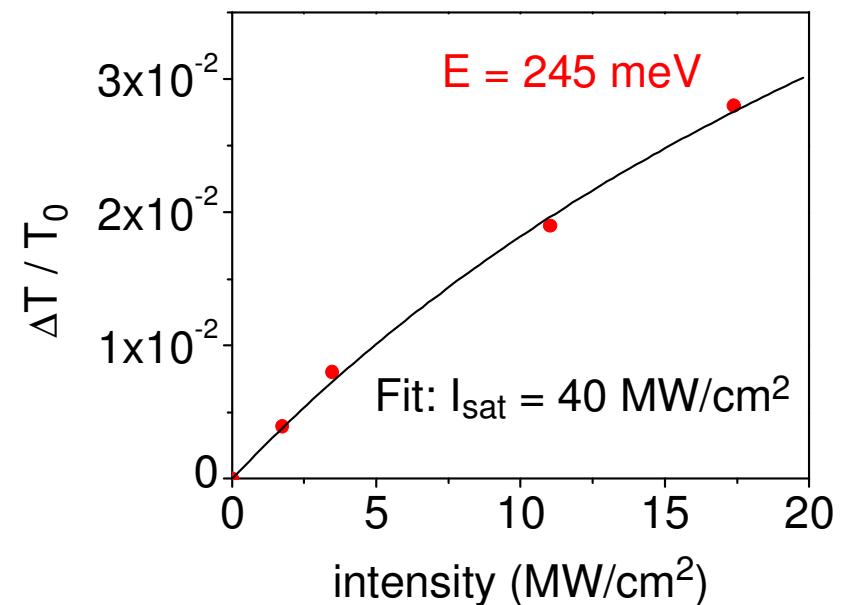
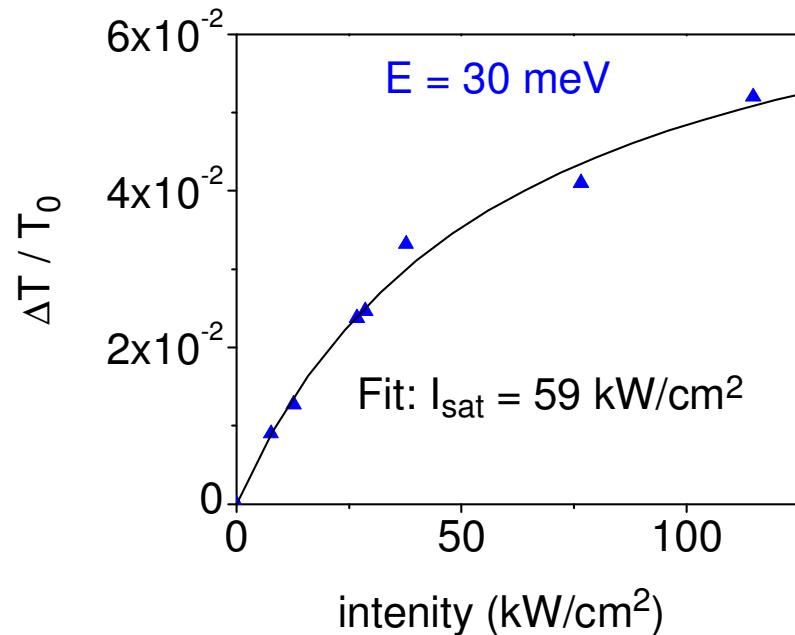
Induced *transmission* for $\hbar\omega > 2|E_F|$
due to Pauli blocking



Induced *absorption* for $\hbar\omega < 2|E_F|$
due to heating of free carriers



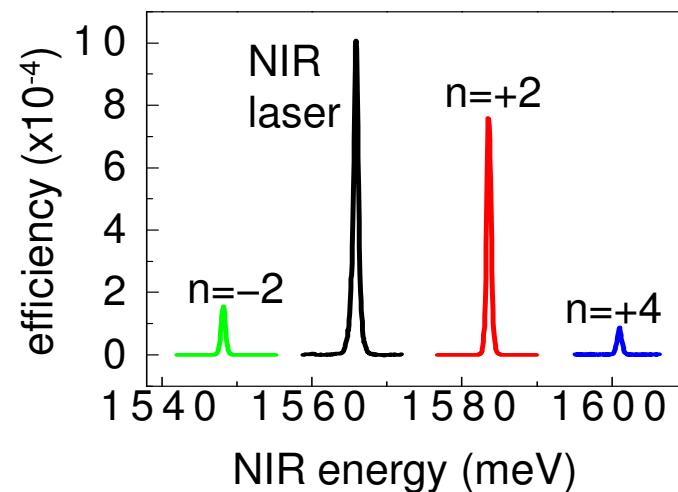
Saturation of the pump-probe signal



$$\Delta T / T_0 \propto \frac{I / I_{\text{sat}}}{1 + I / I_{\text{sat}}}$$

Example for perturbative nonlinear interaction: sideband generation in semiconductor quantum wells

Resonant excitation of excitonic levels



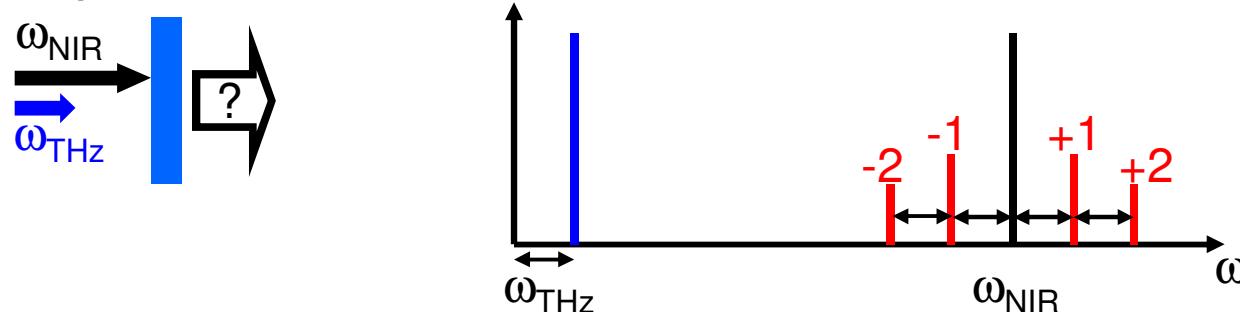


Nonlinear optics in the perturbative regime

$$\begin{aligned} P_i &= \epsilon_0 \sum_j \chi_{ij}^{(1)} E_j + \epsilon_0 \sum_{jk} \chi_{ijk}^{(2)} E_j E_k + \epsilon_0 \sum_{jkl} \chi_{ijkl}^{(3)} E_j E_k E_l + \dots \\ &= P_i^{(1)} + P_i^{(2)} + P_i^{(3)} + \dots \end{aligned}$$

F

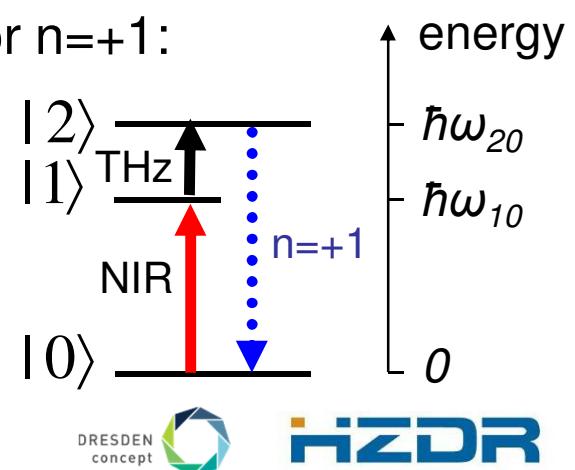
Mixing of NIR and THz waves: **THz sidebands around NIR line**



Efficient sidebands for resonant excitations, e.g. for $n=+1$:

$$\begin{aligned} P^{(2)} &= \epsilon_0 \chi^{(2)} E_{\text{NIR}} E_{\text{THz}} \\ \chi^{(2)} &\propto \sum_{m,v=1,2} \frac{\mu_{0m}^{\text{NIR}} \mu_{mv}^{\text{THz}} \mu_{v0}^{n=+1}}{(\omega_{m0} - \omega_{\text{NIR}} - \omega_{\text{THz}} - i\gamma_{m0})(\omega_{v0} - \omega_{\text{NIR}} - i\gamma_{v0})} \end{aligned}$$

matrix element
line width



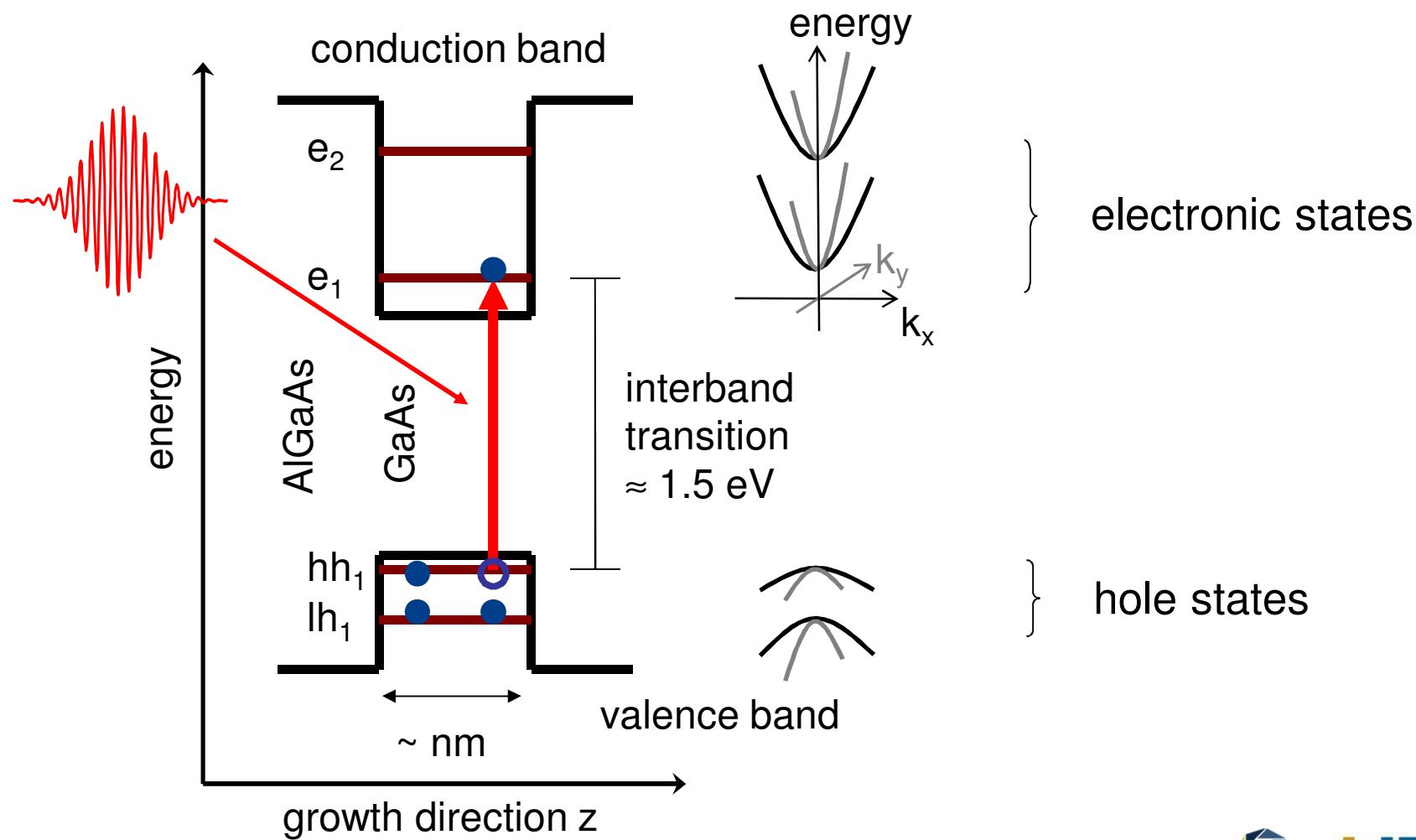
Folie 16

FZD-MA1 FZD Mitarbeiter; 30.03.2012



Electrons in quantum wells, interband excitation

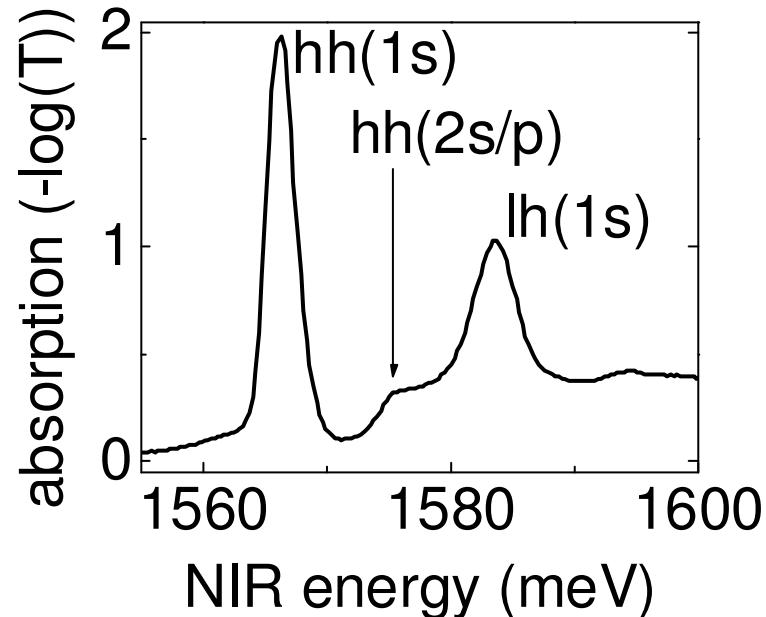
- optical interband excitation





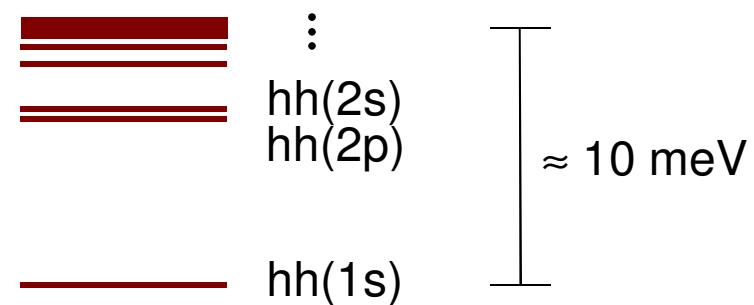
Excitonic energy spectrum

- example: near-infrared absorption



- hydrogen atom like energy structure with binding energies in the THz range
(1 THz = 4.1 meV)

excitons



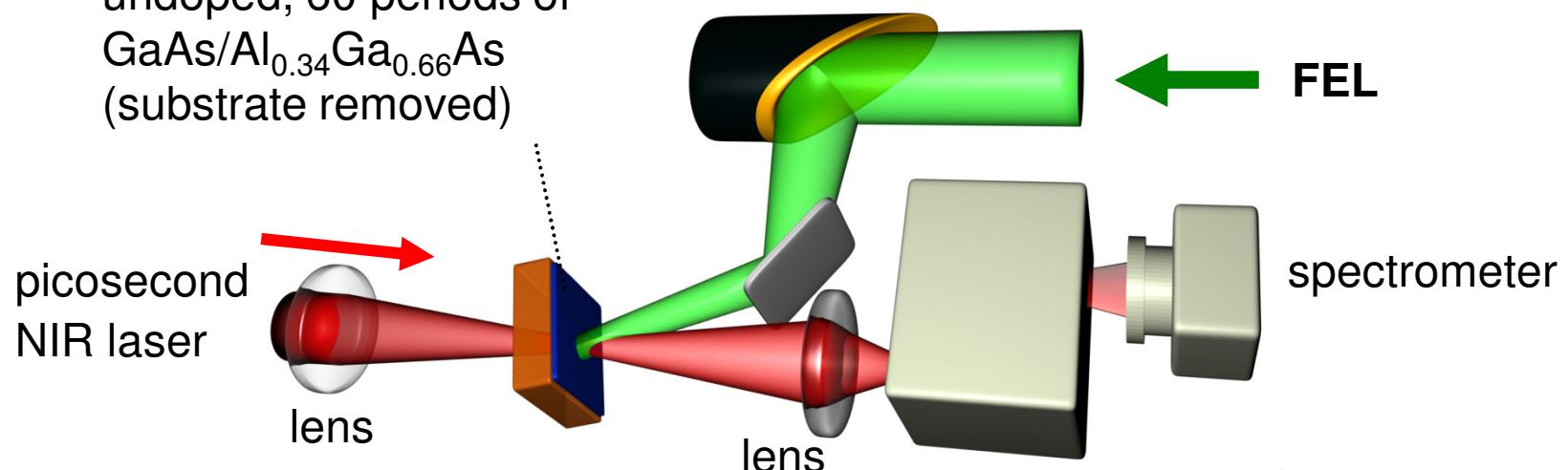
- selection rules:
 - 2p state optically „dark“
 - intraexciton 1s-2p couples to THz



Sideband generation - Experiment

- here:
intraexcitonic sideband generation
using the 1s-2p transition

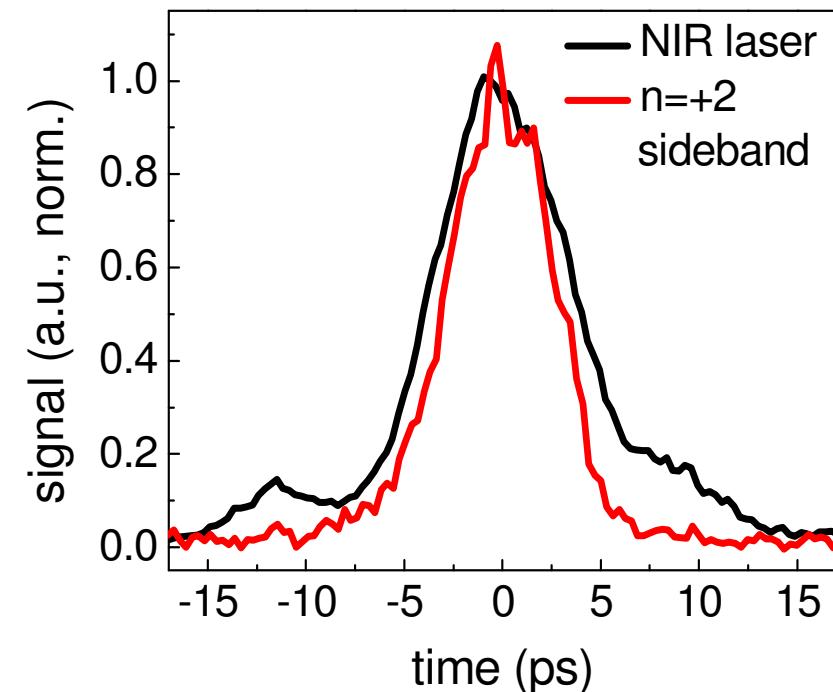
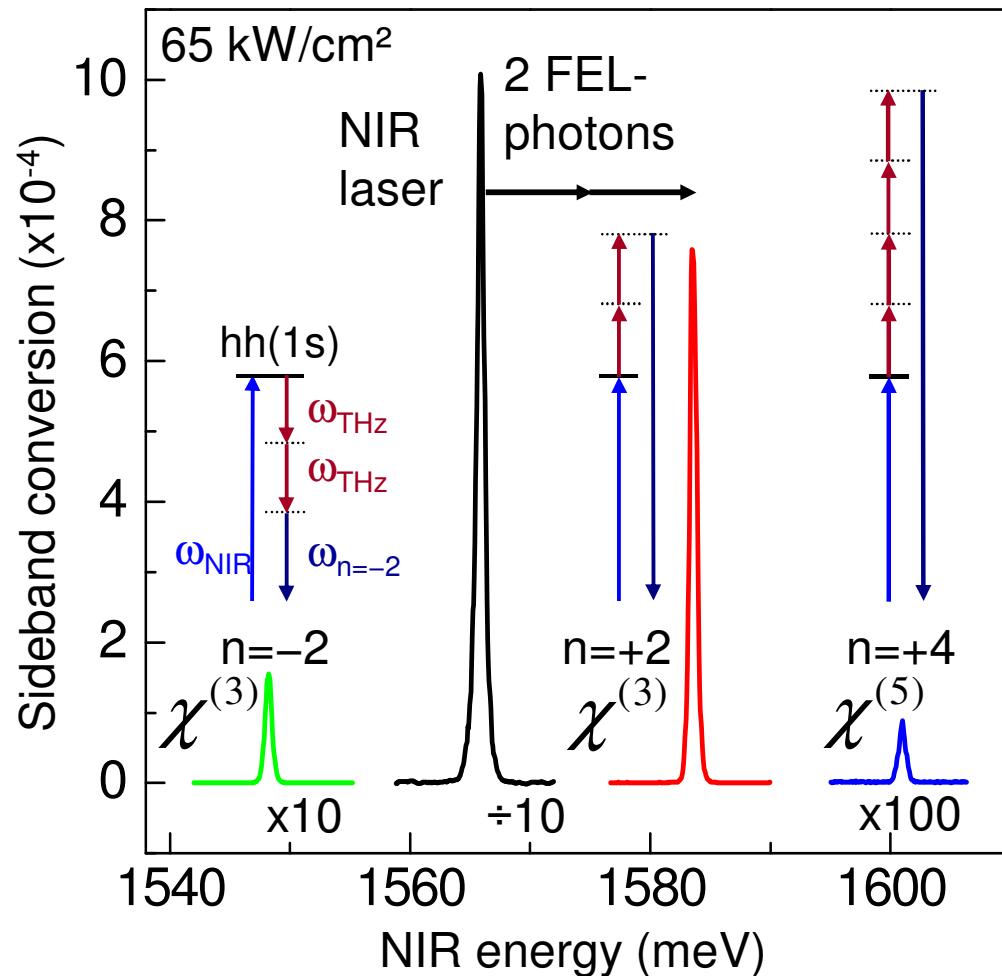
quantum well @ 10 K,
undoped, 60 periods of
 $\text{GaAs}/\text{Al}_{0.34}\text{Ga}_{0.66}\text{As}$
(substrate removed)





Results

- sidebands for NIR laser resonant with hh(1s) exciton and FEL resonant with 1s-2p transition:
- sidebands only at temporal overlap of NIR and THz pulses



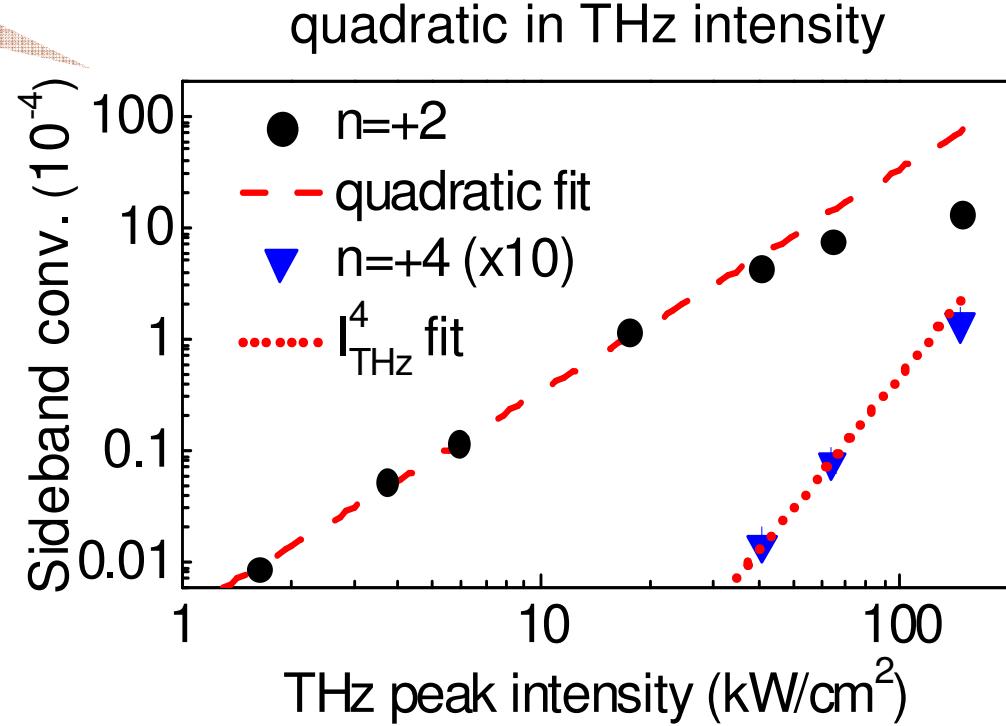
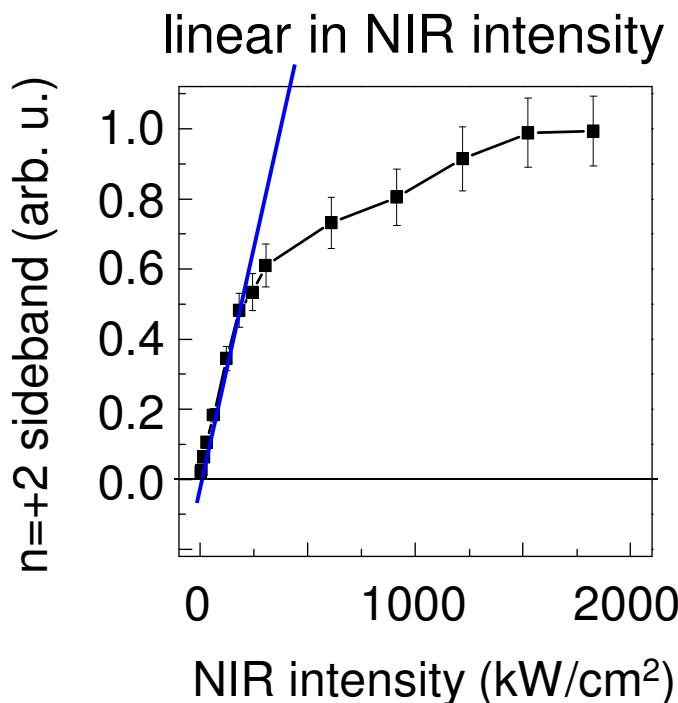
M. Wagner et al., APL **94**, 241105 (2009)



Results

- $n=+2$ sideband signal dependency on THz intensity as expected from

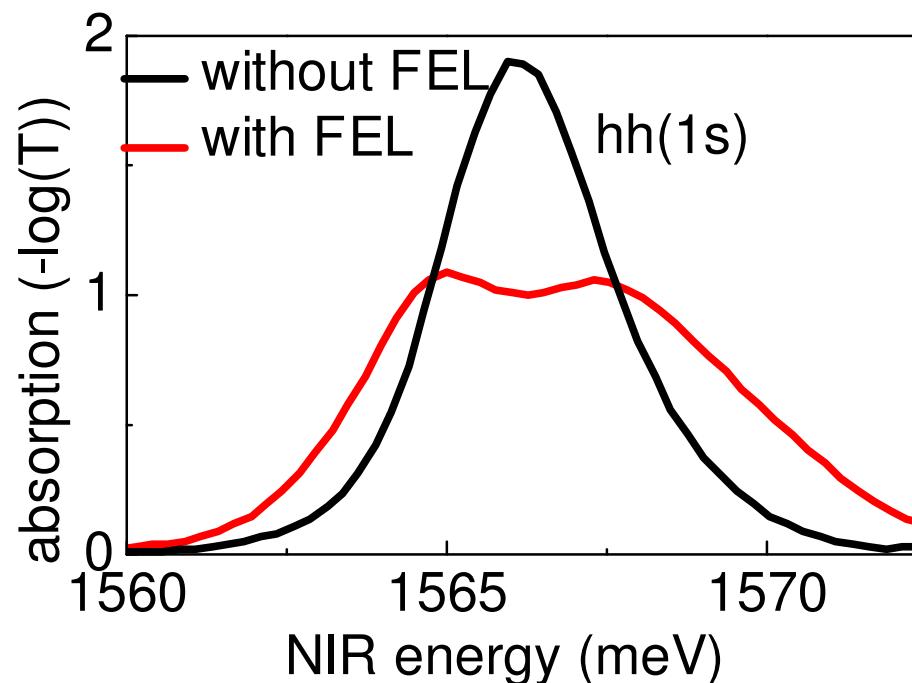
$$P^{(3)} = \epsilon_0 \chi^{(3)} E_{\text{NIR}} E_{\text{FEL}}^2$$



- **high conversion efficiency**
 $> 0.1\%$ in $1.7\text{ }\mu\text{m}$ thin film

Possible application in transfer of THz signals,
optical switches, wavelength division multiplexing...

Example for nonperturbative nonlinear interaction: Intraexcitonic Autler-Townes splitting





Nonlinear optics experiments - AC Stark effect

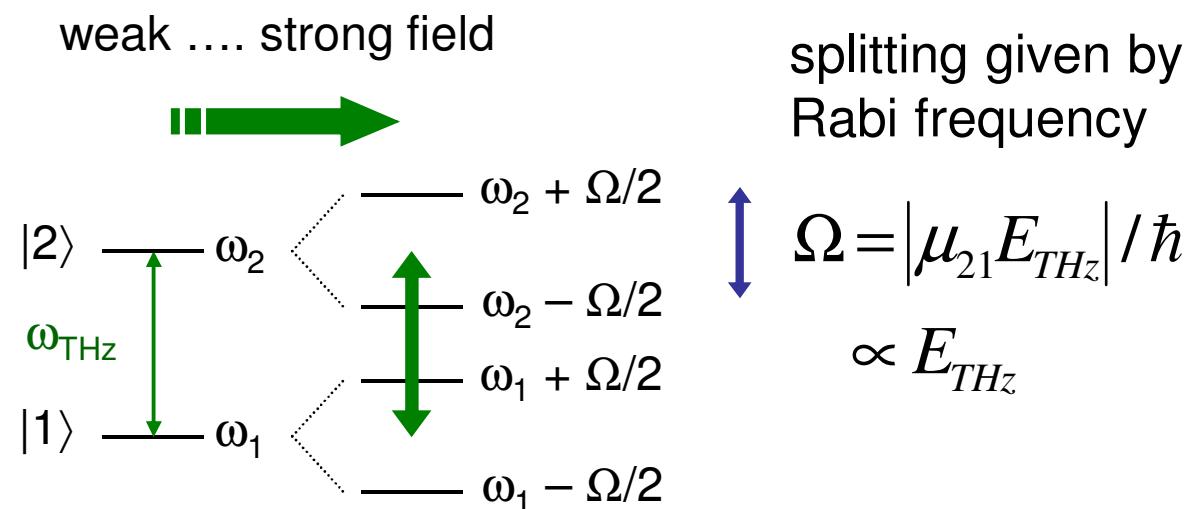
- simplest system to study light-matter interaction:
two levels driven by intense light





Nonlinear optics experiments – Autler-Townes effect

- simplest system to study light-matter interaction:
two levels driven by intense light



→ mixed light-matter states or “dressed“ states
→ Autler-Townes* or AC Stark effect

*S. H. Autler & C. H. Townes, *Phys. Rev.* **100**, 703 (1955)

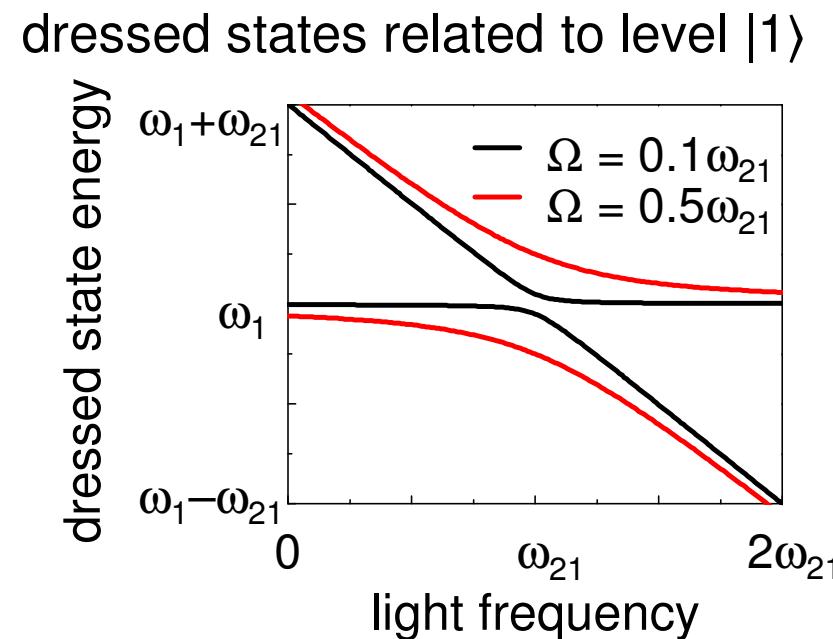


Nonlinear optics experiments - AC Stark effect

- simplest system to study light-matter interaction:
two levels driven by intense light
- solution for two-levels:

$$\begin{aligned}\hbar\omega'_1 &= \hbar \left[\omega_1 - \frac{\Delta}{2} \pm \frac{1}{2} \sqrt{\Delta^2 + \Omega^2} \right] \\ \hbar\omega'_2 &= \hbar \left[\omega_2 + \frac{\Delta}{2} \pm \frac{1}{2} \sqrt{\Delta^2 + \Omega^2} \right]\end{aligned}$$

with $\Delta = \omega - \omega_{21}$ and based on the
rotating-wave approximation,
i.e. $\Omega \ll \omega$

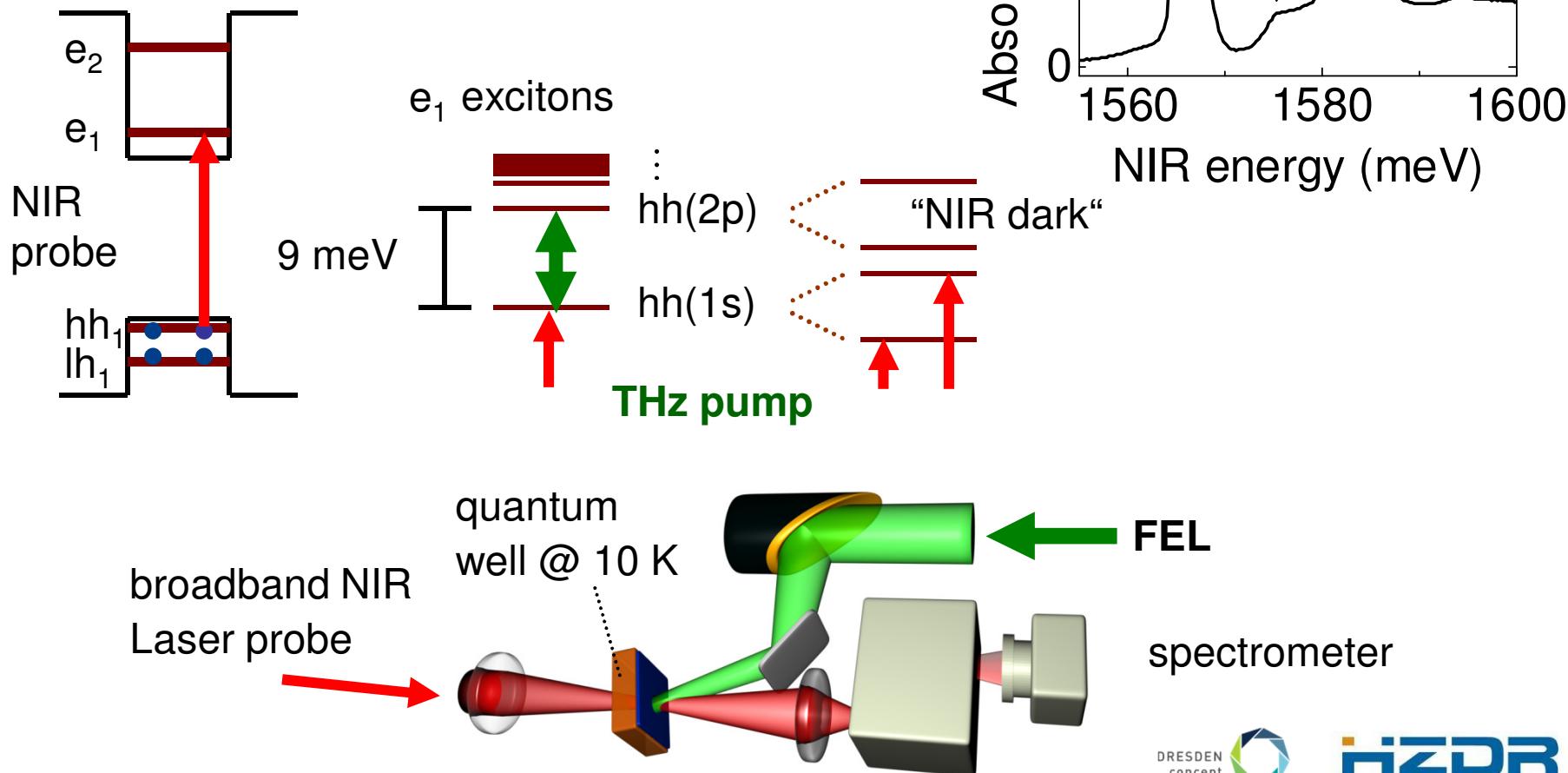


*S. H. Autler & C. H. Townes, *Phys. Rev.* **100**, 703 (1955)



AC Stark effect - Experiment

- here:
intra-excitonic 1s-2p transition
driven by a free-electron laser

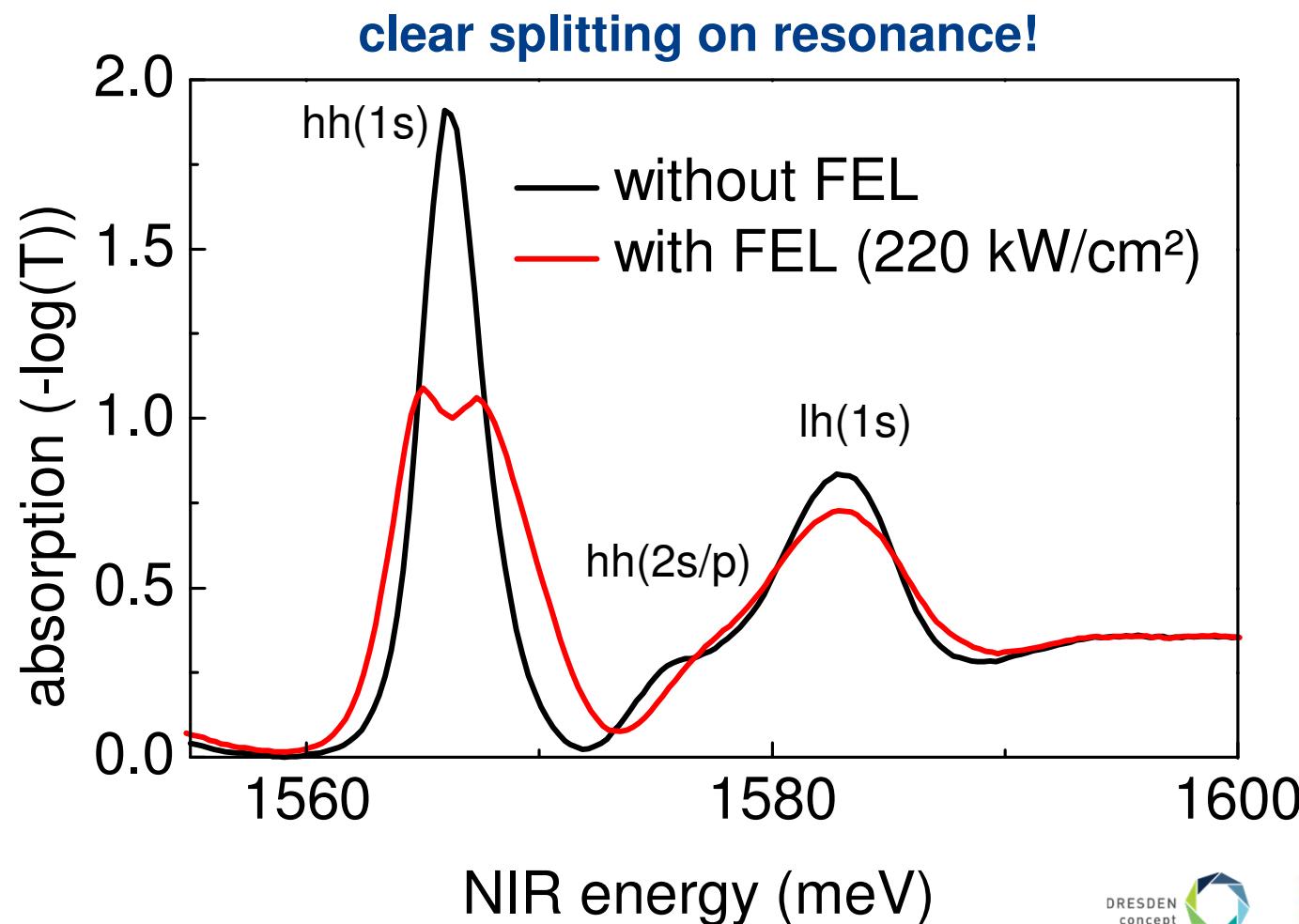
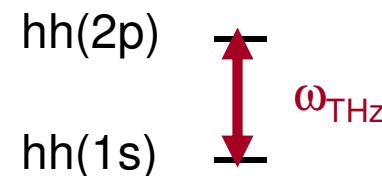




THz modifications of NIR absorption

- near resonance

$$\hbar\omega_{\text{THz}} = 10.5 \text{ meV}$$

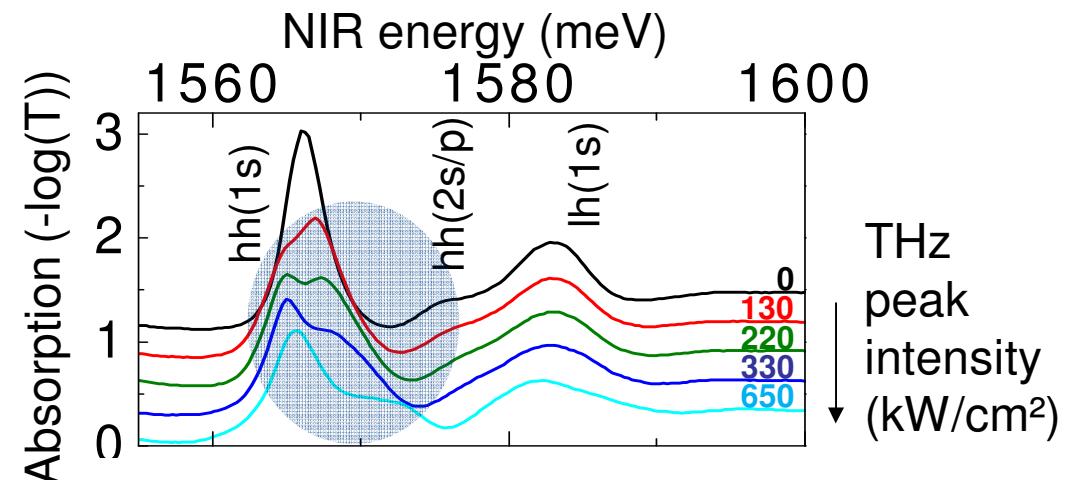
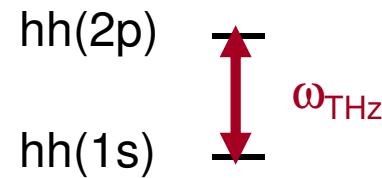




THz modifications of NIR absorption

- near resonance

$$\hbar\omega_{\text{THz}} = 10.5 \text{ meV}$$

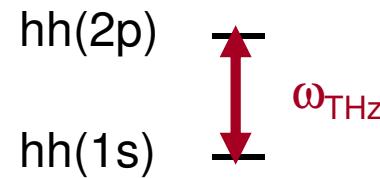




THz modifications of NIR absorption

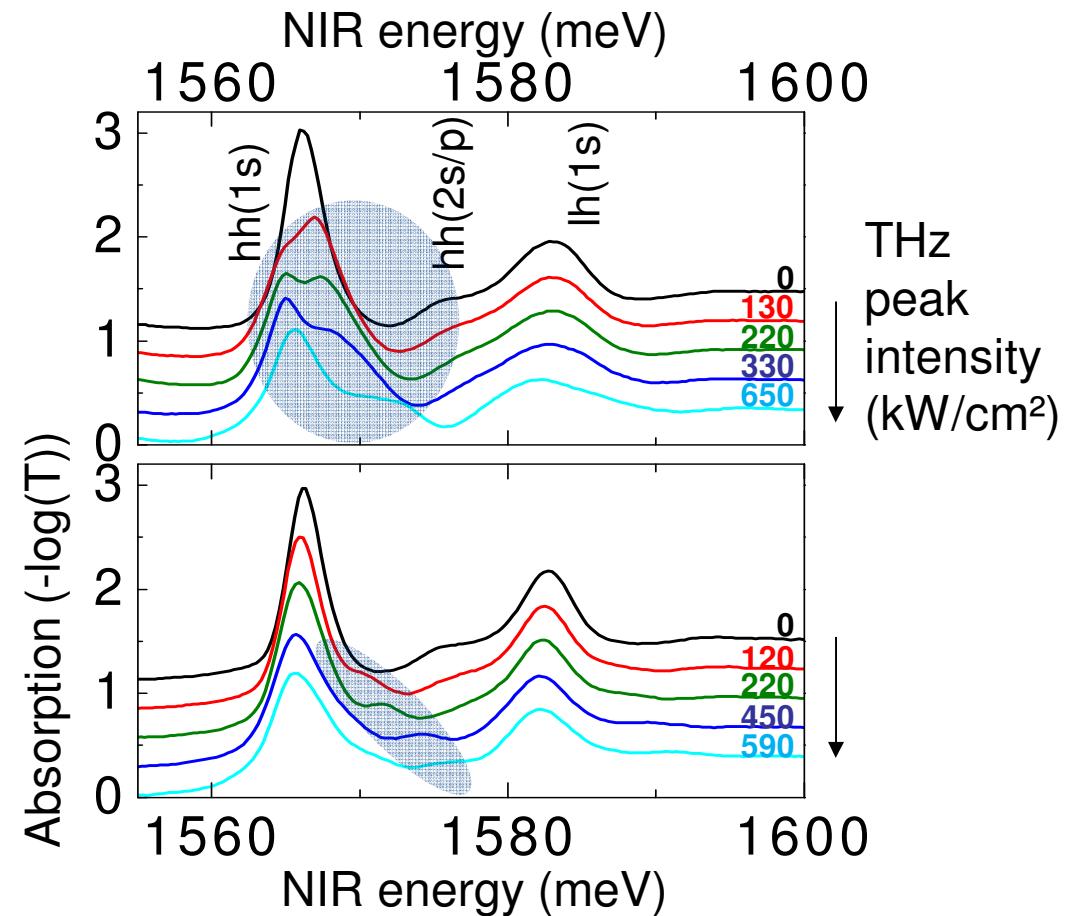
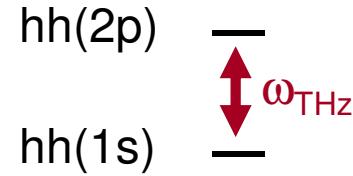
- near resonance

$$\hbar\omega_{\text{THz}} = 10.5 \text{ meV}$$



- below resonance

$$\hbar\omega_{\text{THz}} = 6.1 \text{ meV}$$

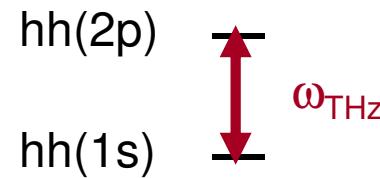




THz modifications of NIR absorption

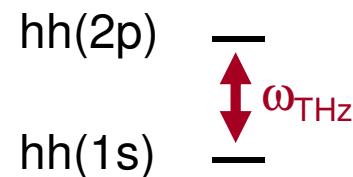
- near resonance

$$\hbar\omega_{\text{THz}} = 10.5 \text{ meV}$$



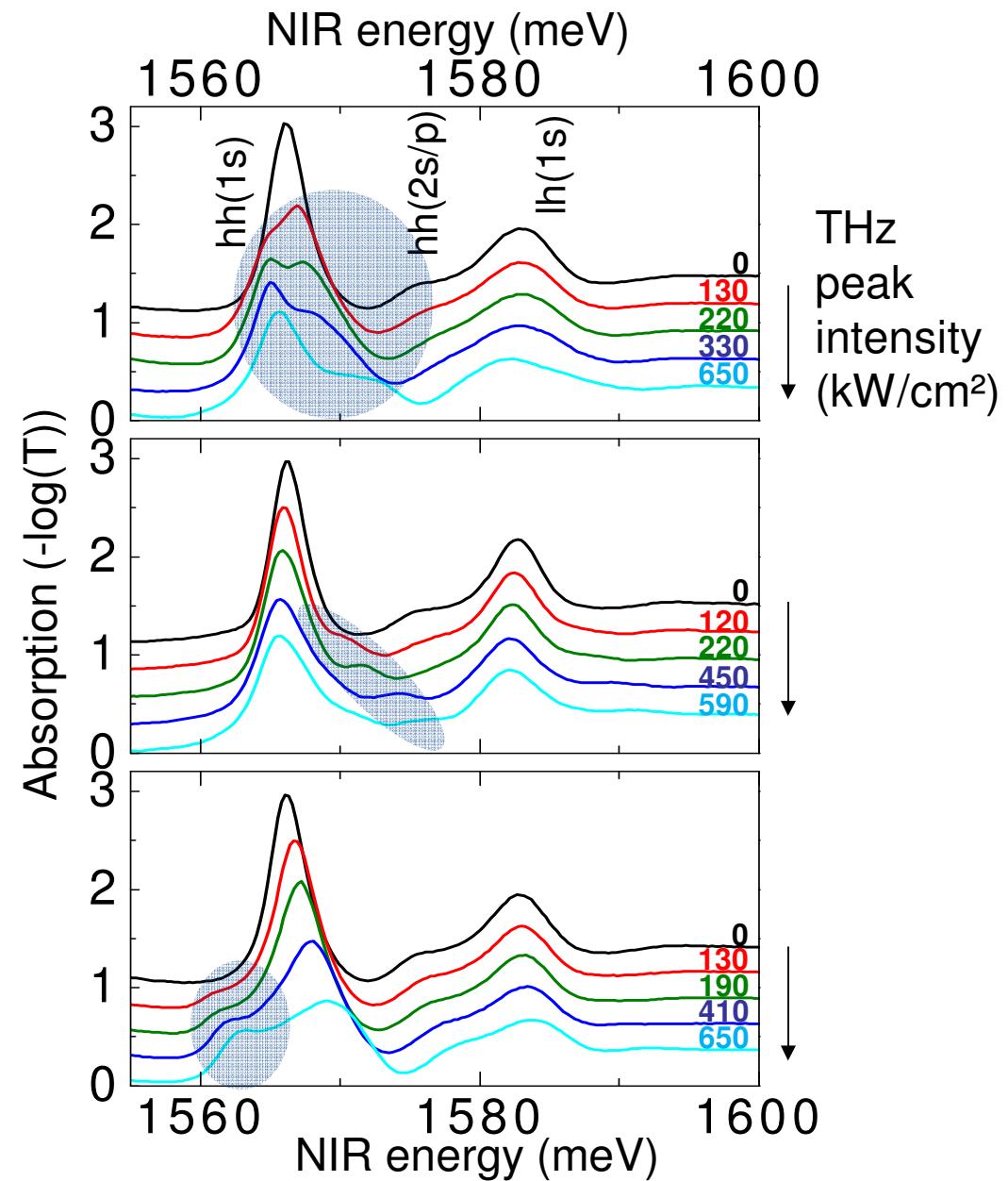
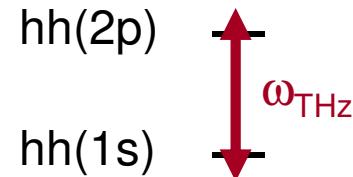
- below resonance

$$\hbar\omega_{\text{THz}} = 6.1 \text{ meV}$$



- above resonance

$$\hbar\omega_{\text{THz}} = 14 \text{ meV}$$

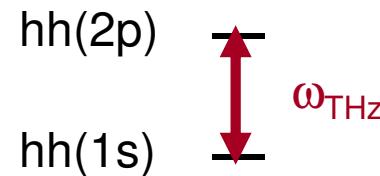




THz modifications of NIR absorption

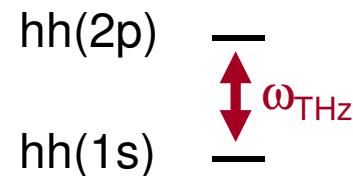
- near resonance

$$\hbar\omega_{\text{THz}} = 10.5 \text{ meV}$$



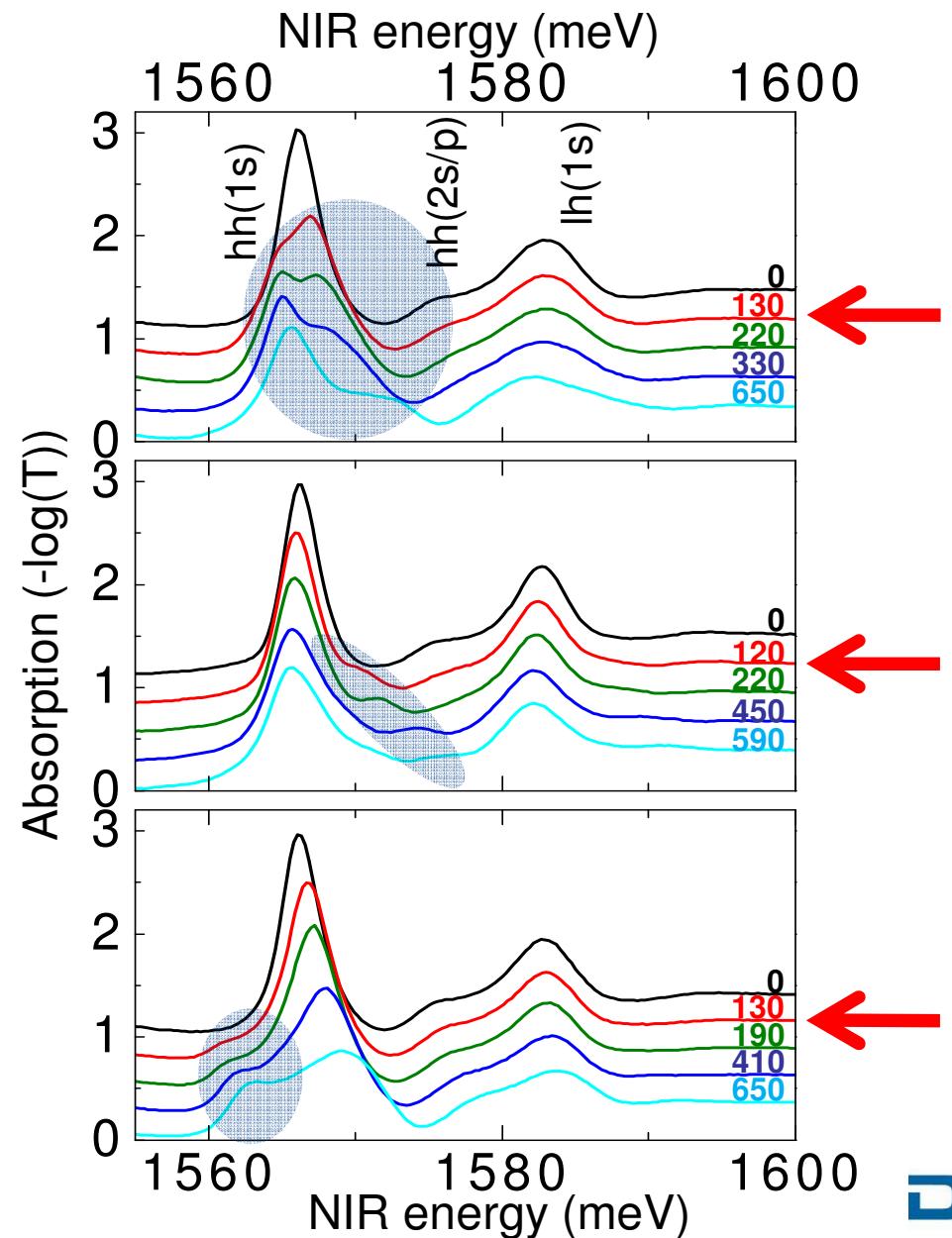
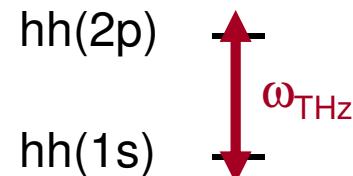
- below resonance

$$\hbar\omega_{\text{THz}} = 6.1 \text{ meV}$$



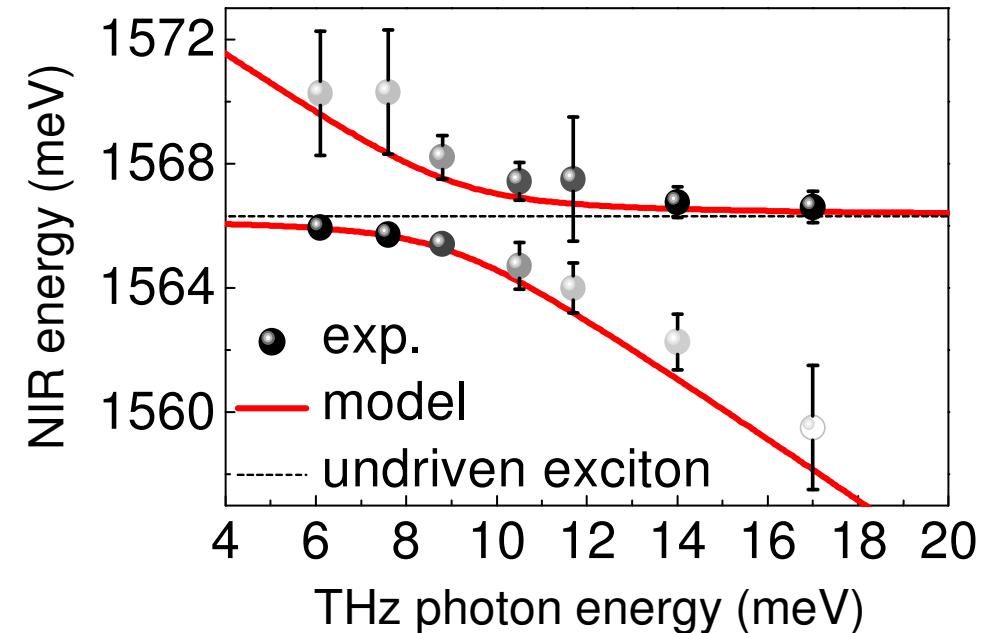
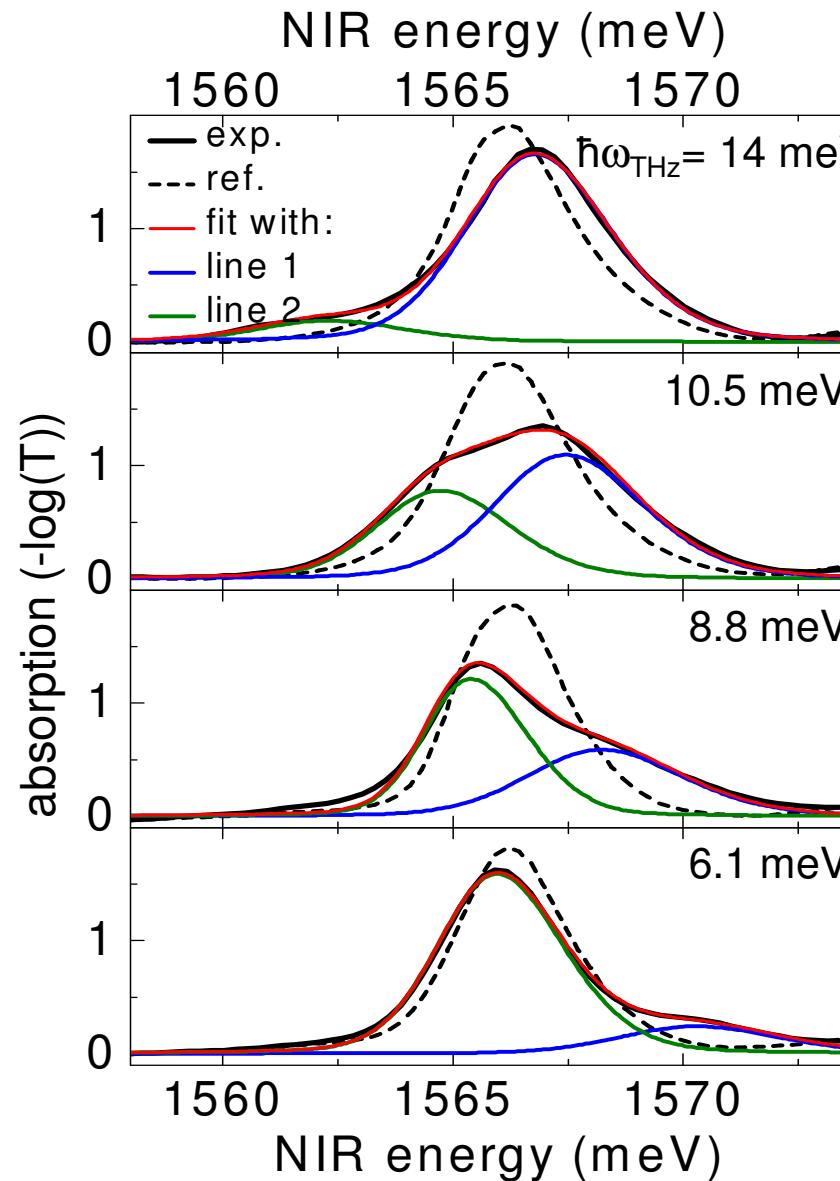
- above resonance

$$\hbar\omega_{\text{THz}} = 14 \text{ meV}$$





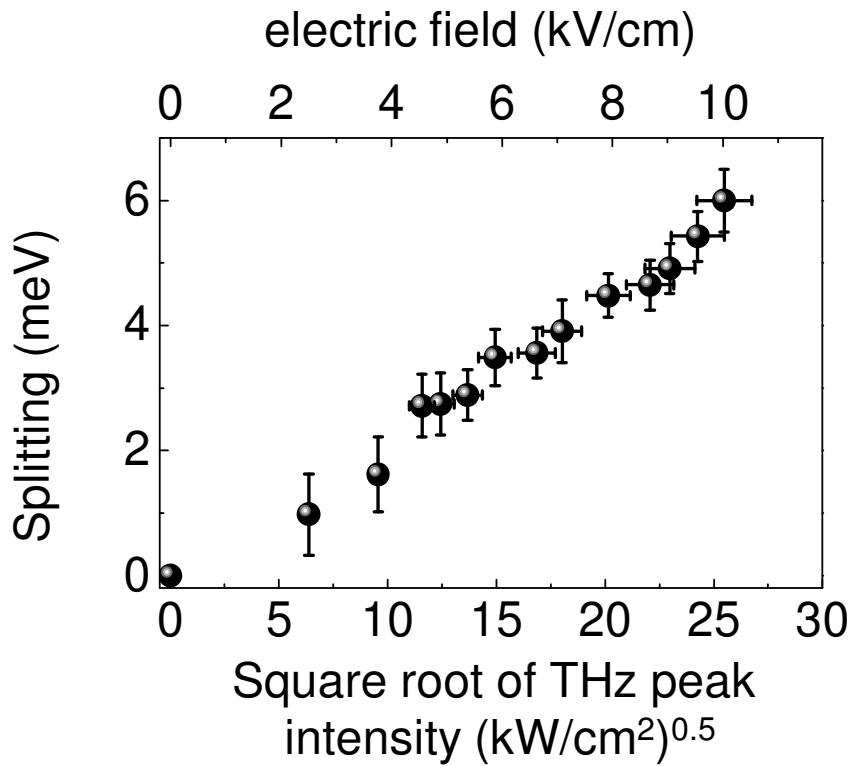
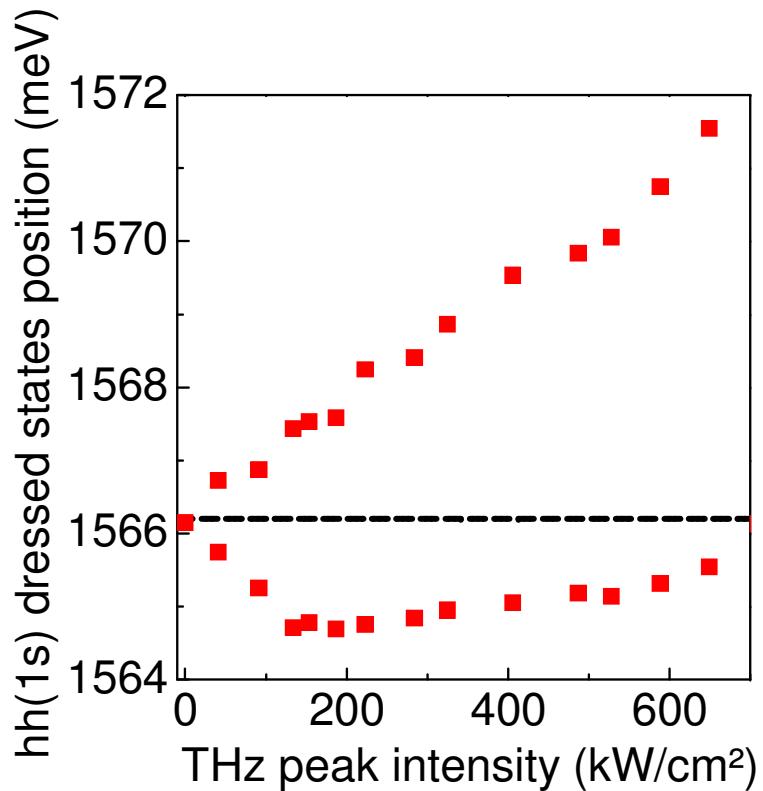
hh(1s) absorption for different THz photon energies



→ clear anticrossing
(130 kW/cm^2 , 4.4 kV/cm)
at 1s-2p resonance (9 meV)



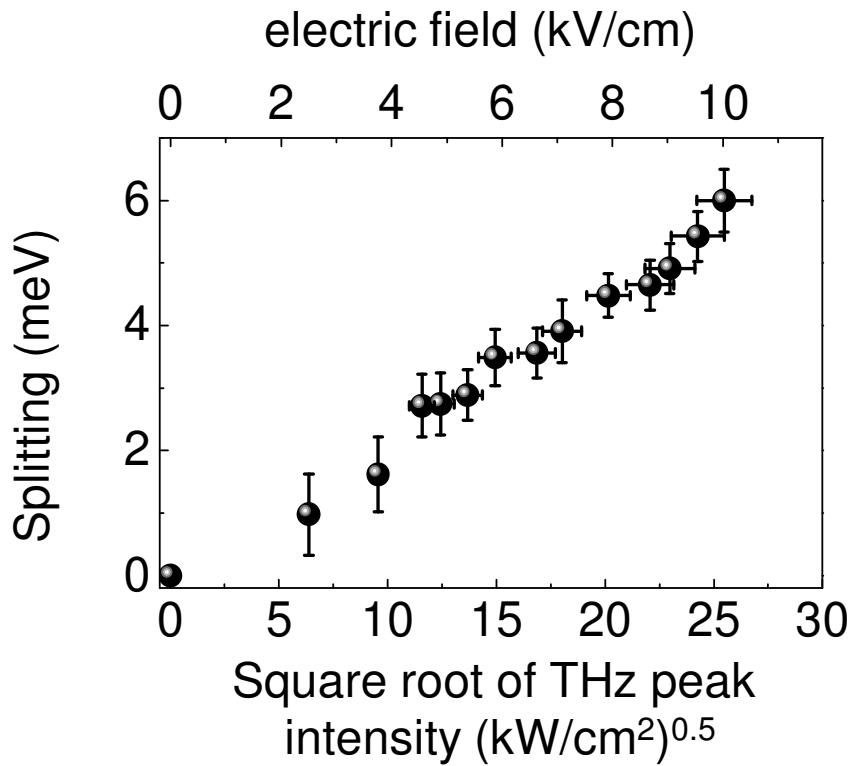
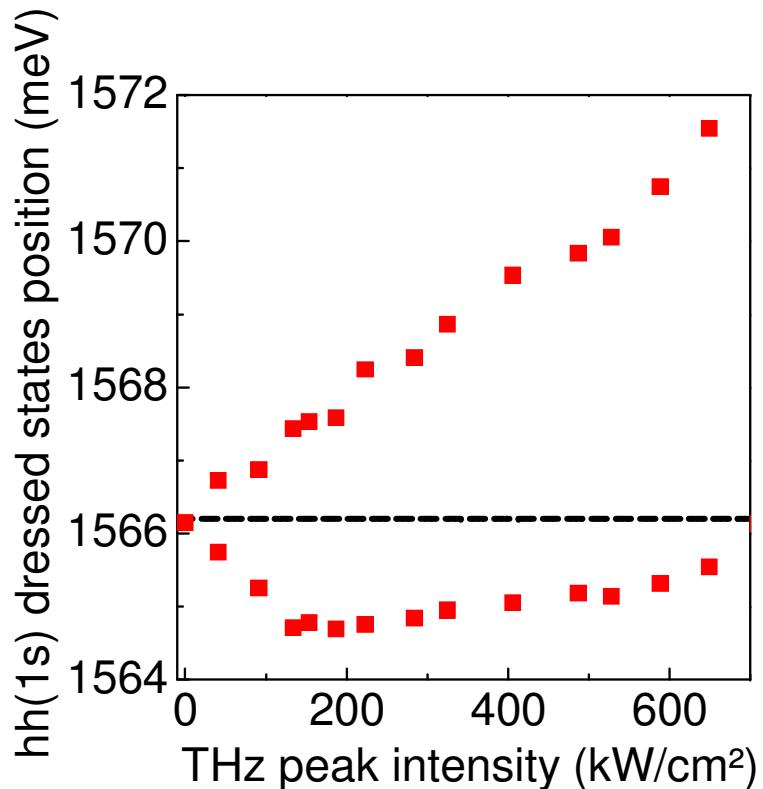
Splitting on resonance



- splitting increases linearly with field up to $650 \text{ kW}/\text{cm}^2$ ($10 \text{ kV}/\text{cm}$)
- estimated splitting (from matrix element) @ $200 \text{ kW}/\text{cm}^2$, $5.4 \text{ kV}/\text{cm}$: 2.4 meV compared to 3 meV measured → good agreement



Splitting on resonance

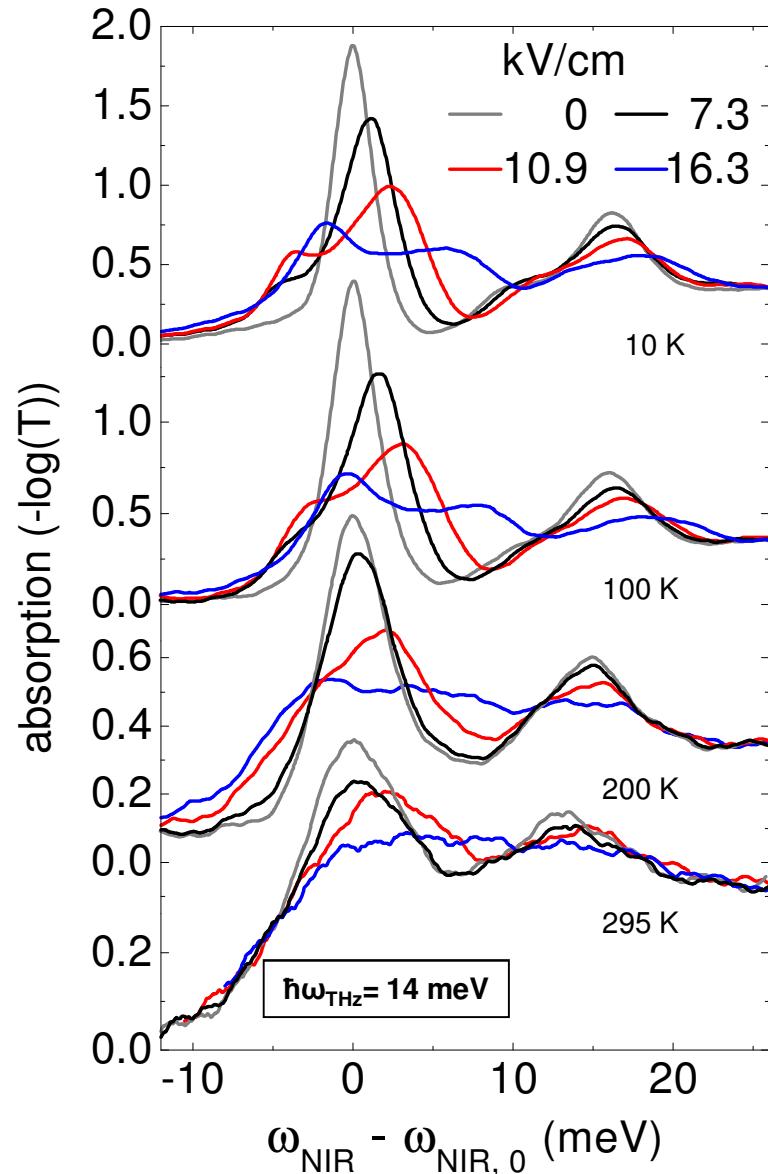


- important values @ 10 kV/cm:
 - 1s-2p transition energy 9 meV
 - THz photon energy 10.5 meV
 - splitting 6 meV
 - ponderomotive energy $U_p = 3$ meV

M. Wagner *et al.*, PRL 105,
167401 (2010)



Temperature dependence



Substantial NIR transmission change
(at 200 K still threefold NIR transmission
change)
→ optical modulator application with
Peltier-cooling

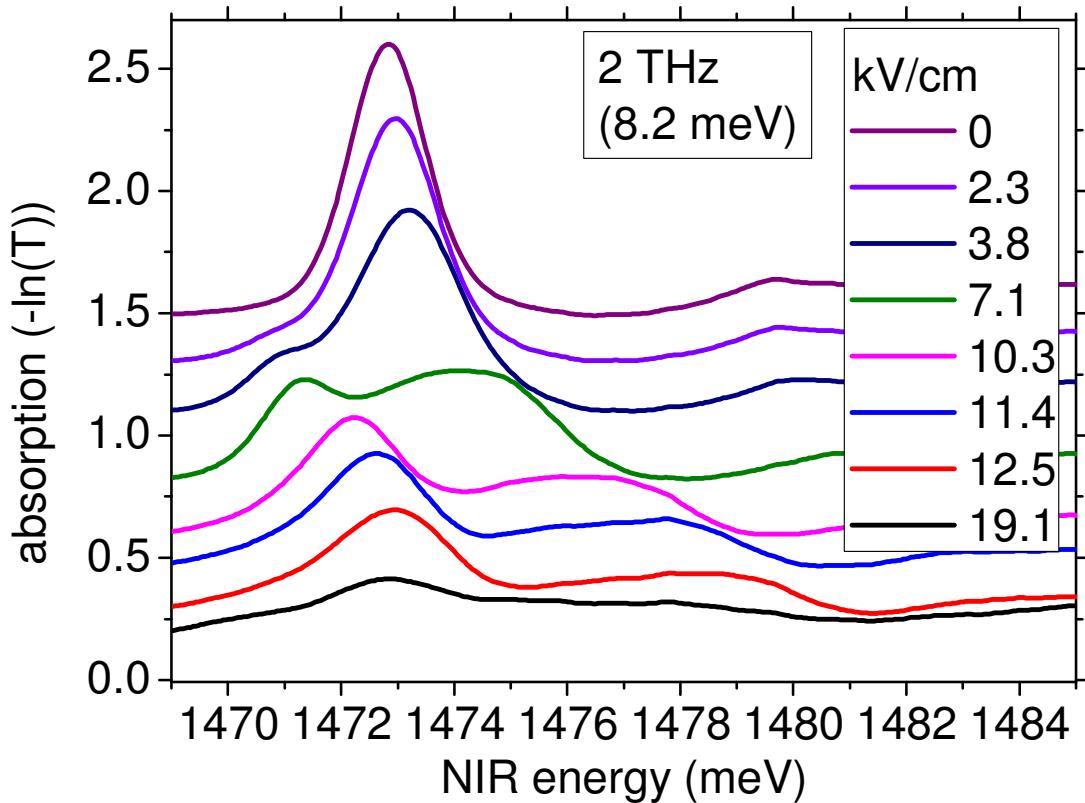
Poster:
Martin Teich

M. Wagner et al., APL 100, 051109 (2012)





What happens at even higher intensities (up to 1.75 MW/cm²)



InGaAs quantum wells
With narrow linewidth

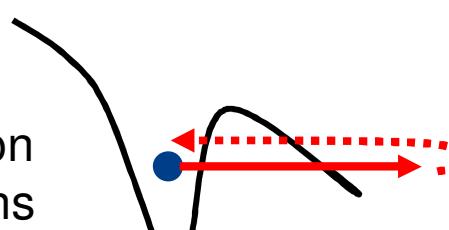
Features not explained by
two-level model and RWA:
- relative peak intensities
- overall blueshift
- broadening of peaks

Here: extreme nonlinear
optics accessible beyond
rotating-wave regime, where

$$U_p \approx E_{binding} \approx \hbar\omega_{THz} \approx \Omega$$

Outlook:

- high-harmonic generation
- field ionization of excitons



B. Zaks et al., Nature **483**, 580 (2012)

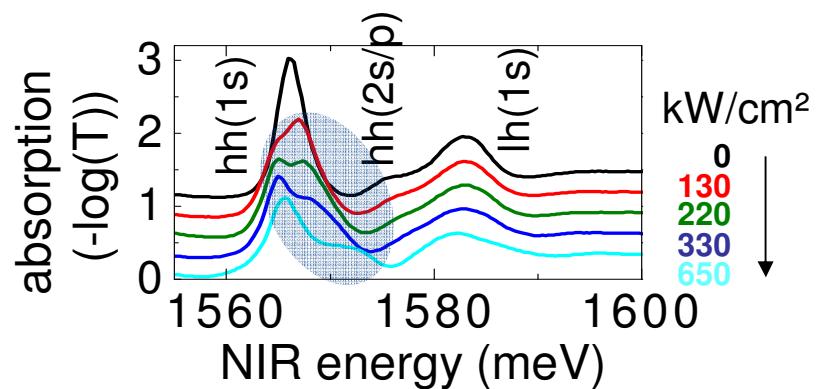
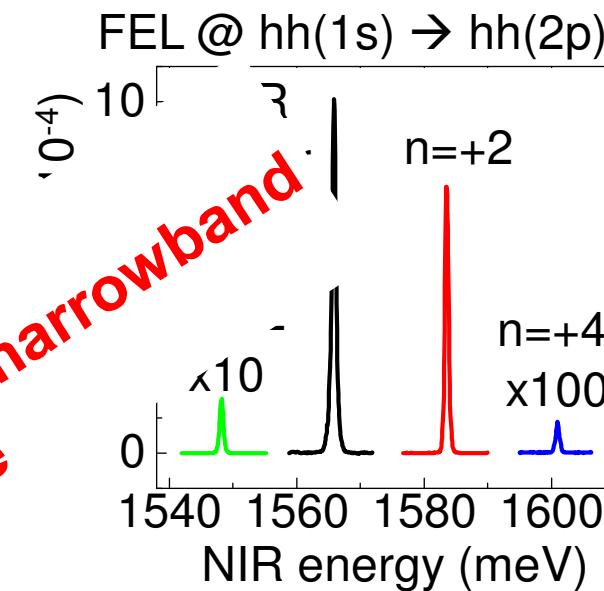
E. Ewers et al., Phys. Rev. B **85**, 075307 (2012)



Summary

- Pump-probe spectroscopy on graphene
 - saturation of the signals
 - population dynamics
- Efficient sideband generation
 - perturbative nonlinear optics
- Autler-Townes splitting even at elevated T
- extreme nonlinear effects accessible beyond rotating-wave regime where $U_p \approx E_{binding} \approx \hbar\omega_{THz} \approx \Omega$

FEL:
tunable, intense and narrowband source





Acknowledgement

HZDR

M. Wagner

M. Teich

D. Stehr

M. Mittendorff

H. Schneider

M. Helm

P. Michel and
ELBE Team

Univ. Marburg

S. Chatterjee

S. W. Koch

CNRS Grenoble

M. Orlita

M. Potemski

TU Berlin

T. Winzer

E. Malic

A. Knorr

Univ. Arizona

H. Gibbs

G. Khitrova

Thank you for your attention!

Samples:

TU Vienna

T. Roch

A. M. Andrews

S. Schartner

G. Strasser

Georgia Tech

M. Sprinkle

C. Berger

W. A. de Heer

DFG

Deutsche
Forschungsgemeinschaft



HZDR

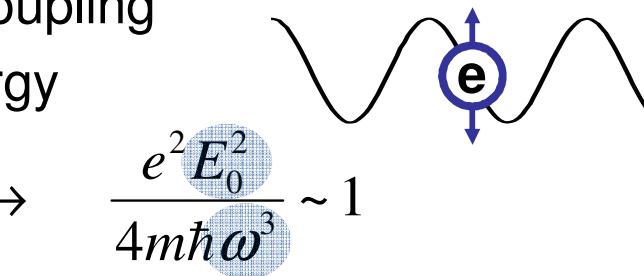


Motivation

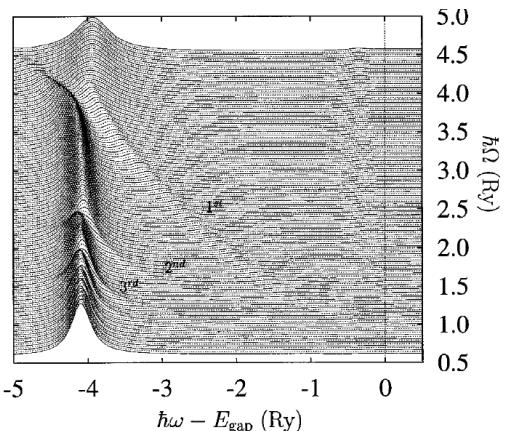
- energy/frequency ranges in light-matter coupling
- ponderomotive energy \sim THz photon energy

$$\frac{1}{T} \int_0^T \left(\frac{1}{2} m v^2 \right) dt = \frac{e^2 E_0^2}{4m\omega^2} = U_p \sim \hbar\omega \leftrightarrow \frac{e^2 E_0^2}{4m\hbar\omega^3} \sim 1$$

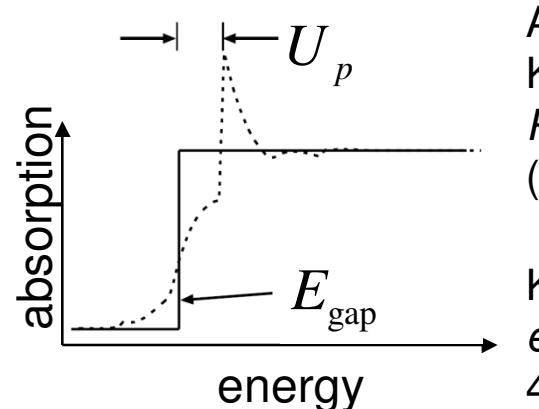
→ AC Stark effect, Rabi oscillations
sidebands (require resonant driving)



dynamical Franz-Keldysh effect



K. Johnsen
and A. P.
Jauho,
PRL **83**, 1207
(1999)



A. P. Jauho &
K. Johnsen,
PRL **76**, 4576
(1996)

K. Nordstrom
et al., *PRL* **81**,
457 (1998)

→ conditions easily met at **THz frequencies** (1 THz = 4.1 meV) for
excitons as artificial atoms with $E_{\text{binding}} \approx 10$ meV

- even extreme nonlinear optics possible:

Rabi energy $\hbar\Omega = \mu E_{\text{THz}} \sim \hbar\omega_{\text{THz}}$

O. D. Mücke *et al.*, *PRL* **87**, 057401 (2001)